US009361993B1

(12) **United States Patent**
Chen et al.

(10) **Patent No.: US 9,361,993 B1**
(45) **Date of Patent: Jun. 7, 2016**

(54) **METHOD OF REDUCING HOT ELECTRON INJECTION TYPE OF READ DISTURB IN MEMORY**

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(73) Assignee: **SanDisk Technologies Inc.**, Plano, TX (US)

(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

(21) Appl. No.: **14/601,531**

(22) Filed: **Jan. 21, 2015**

(51) **Int. Cl.**
G11C 19/08 (2006.01)
G11C 16/26 (2006.01)
G11C 16/04 (2006.01)

(52) **U.S. Cl.**
CPC ***G11C 16/26*** (2013.01); ***G11C 16/0483*** (2013.01)

(58) **Field of Classification Search**
CPC G11C 16/26
USPC 365/185.01–185.33
See application file for complete search history.

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2013/0250690	A1 *	9/2013	Lai	G11C 11/5628 365/185.17

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Primary Examiner — Richard Elms
Assistant Examiner — Sultana Begum
(74) *Attorney, Agent, or Firm* — Vierra Magen Marcus LLP

(57) **ABSTRACT**

Read disturb is reduced in a charge-trapping memory device such as a 3D memory device by optimizing the channel boosting voltage in an unselected NAND string. A pass voltage applied to the unselected word lines can cause a large gradient in the channel which leads to electron-hole formation and a hot electron injection (HEI) type of read disturb. When the selected word line is close to the source-side of the NAND string, HEI disturb occurs on the drain-side of the selected word line. To avoid this disturb, a spike is provided in the control gate voltage of a drain-side selected gate transistor to temporarily connect the channel to the bit line, lowering the voltage of the associated channel region. A similar approach is used for a drain-side selected word line. The spike may be omitted when the selected word line is mid-range.

21 Claims, 20 Drawing Sheets

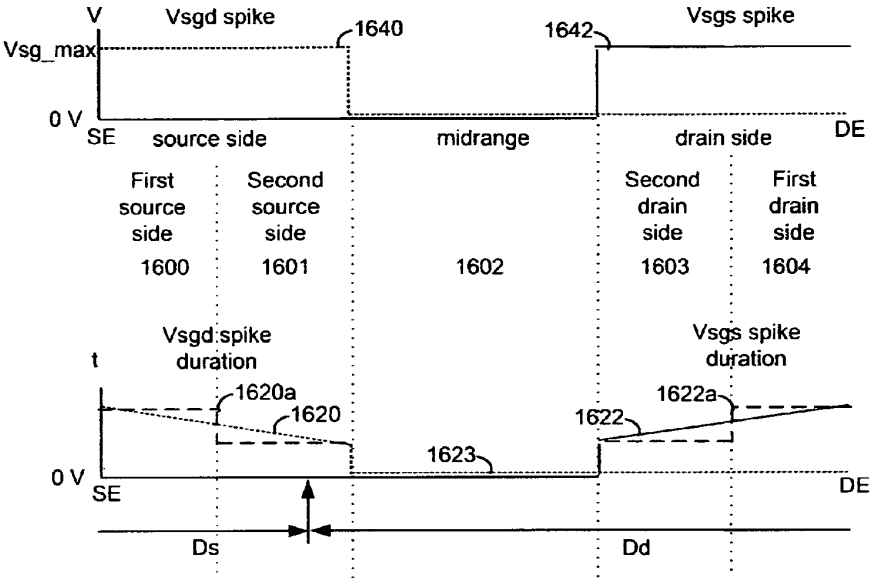


Fig. 1A

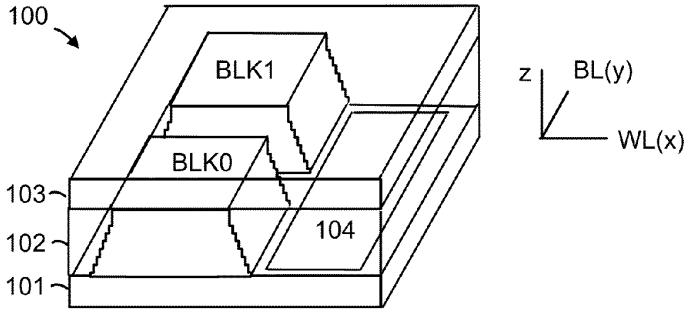

100
BLK1
BLK0
103
102
101
104
z
BL(y)
WL(x)

Fig. 1B

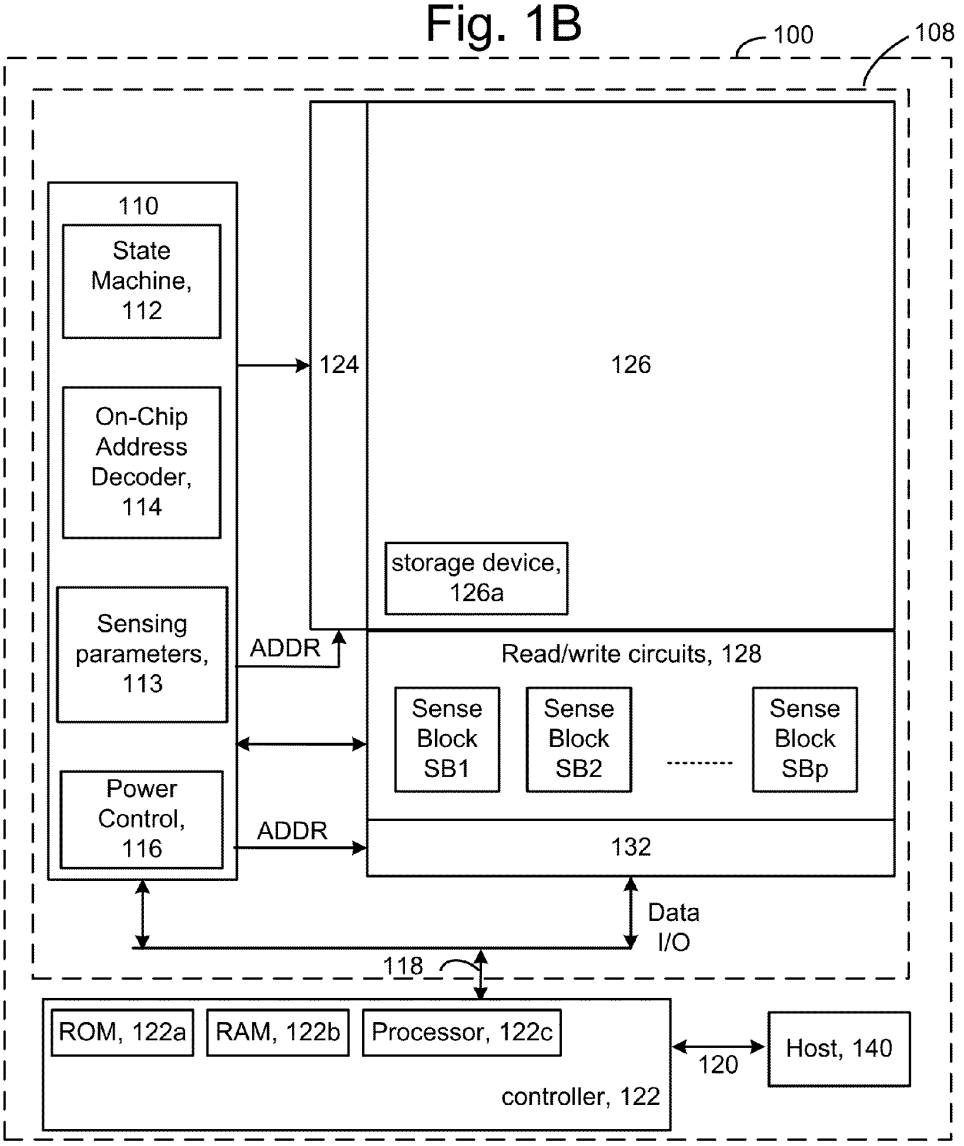

100
108
110
State Machine, 112
On-Chip Address Decoder, 114
Sensing parameters, 113
Power Control, 116
124
126
storage device, 126a
ADDR
Read/write circuits, 128
Sense Block SB1
Sense Block SB2
Sense Block SBp
ADDR
132
Data I/O
118
ROM, 122a
RAM, 122b
Processor, 122c
controller, 122
120
Host, 140

Fig. 1C

Code in storage device (150)

boot code (151)

control code / set of instructions (160)

instructions to apply an increasing voltage to unselected memory cells in unselected levels of a memory device in connection with a sensing operation (161)

instructions to control a select gate of an unselected NAND string to, at different times during the applying of the increasing voltage, allow a driven voltage on a bit line to reach a channel of the unselected NAND string and prevent the driven voltage on the bit line from reaching the channel of the unselected NAND string (162)

instructions to sense a current in the selected NAND string via the bit line while the boosting level is set in the channel of the unselected NAND string (163)

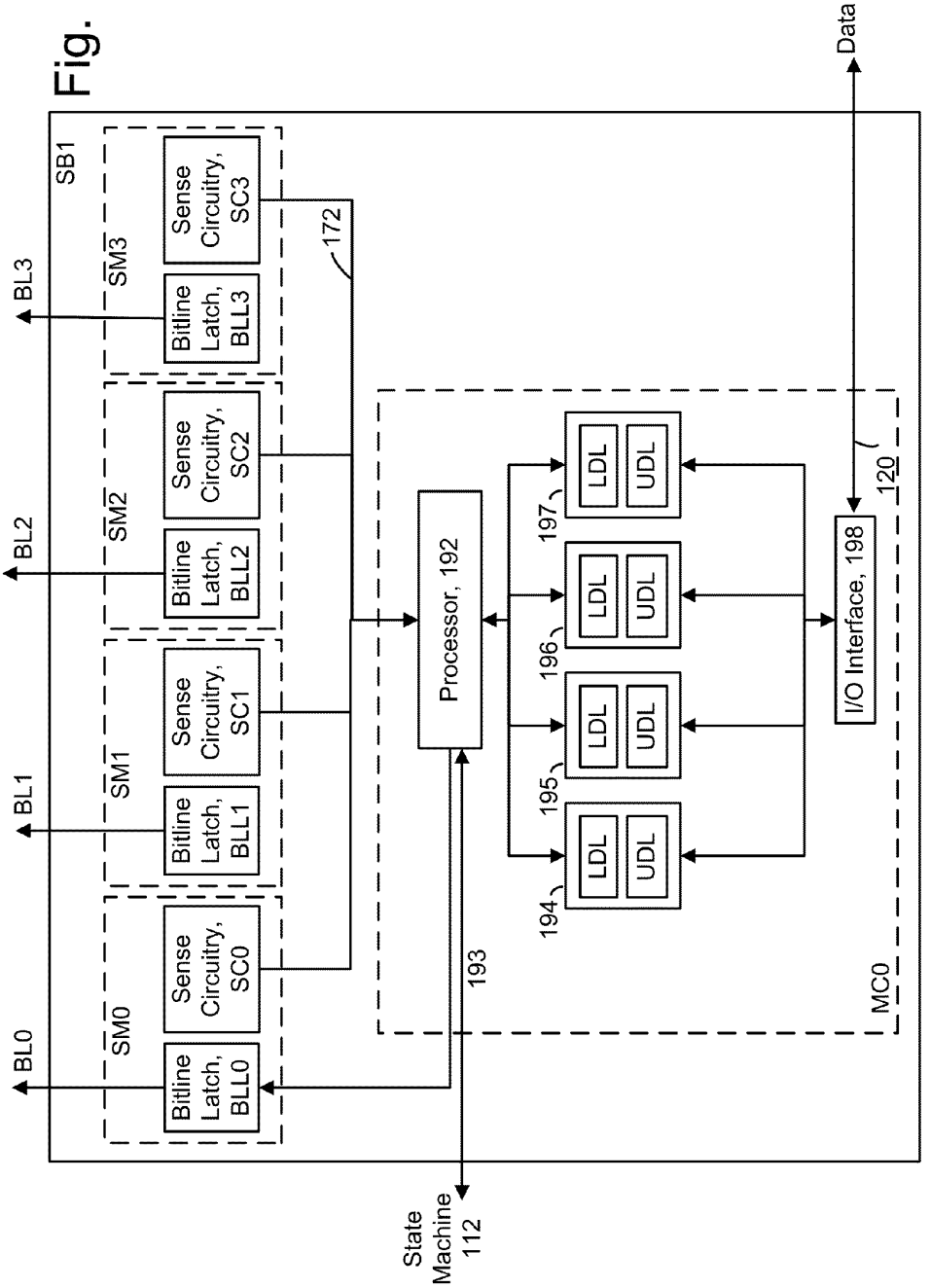

BL0
BL1
BL2
BL3
SB1
SM0
SM1
SM2
SM3
Bitline Latch, BLL0
Bitline Latch, BLL1
Bitline Latch, BLL2
Bitline Latch, BLL3
Sense Circuitry, SC0
Sense Circuitry, SC1
Sense Circuitry, SC2
Sense Circuitry, SC3
172
Processor, 192
193
State Machine 112
194
195
196
197
LDL
UDL
I/O Interface, 198
120
MC0
Data

Fig. 1D

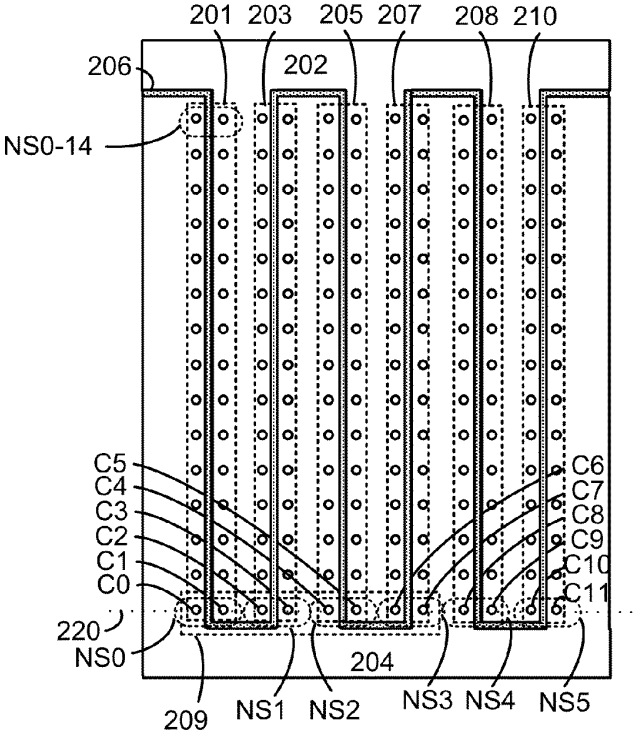

201
203
205
207
208
210
206
202
NS0-14
C5
C4
C3
C2
C1
C0
C6
C7
C8
C9
C10
C11
220
NS0
204
209
NS1
NS2
NS3
NS4
NS5
y
x

Fig. 2A

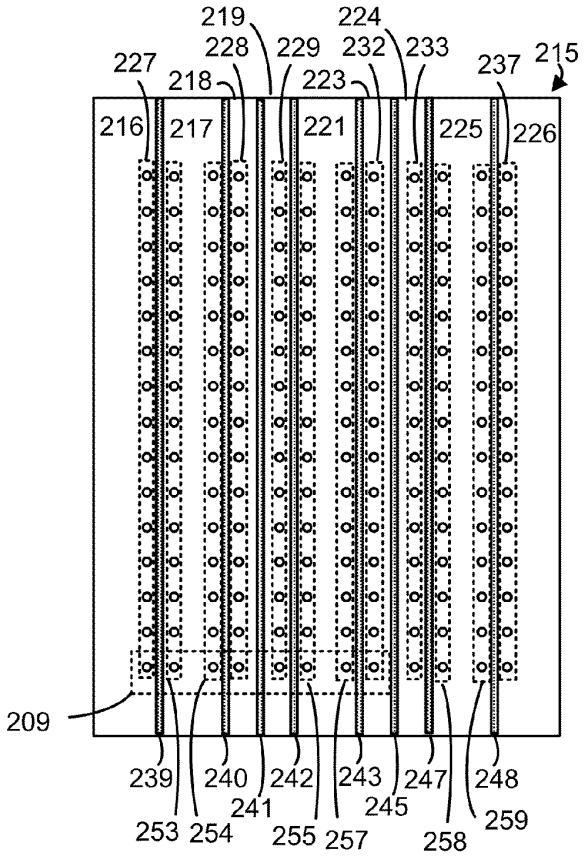

219
224
227
228
229
232
233
237
215
218
223
216
217
221
225
226
209
239
240
242
243
247
248
241
245
253
254
255
257
258
259
y
x

Fig. 2B

Fig. 2C

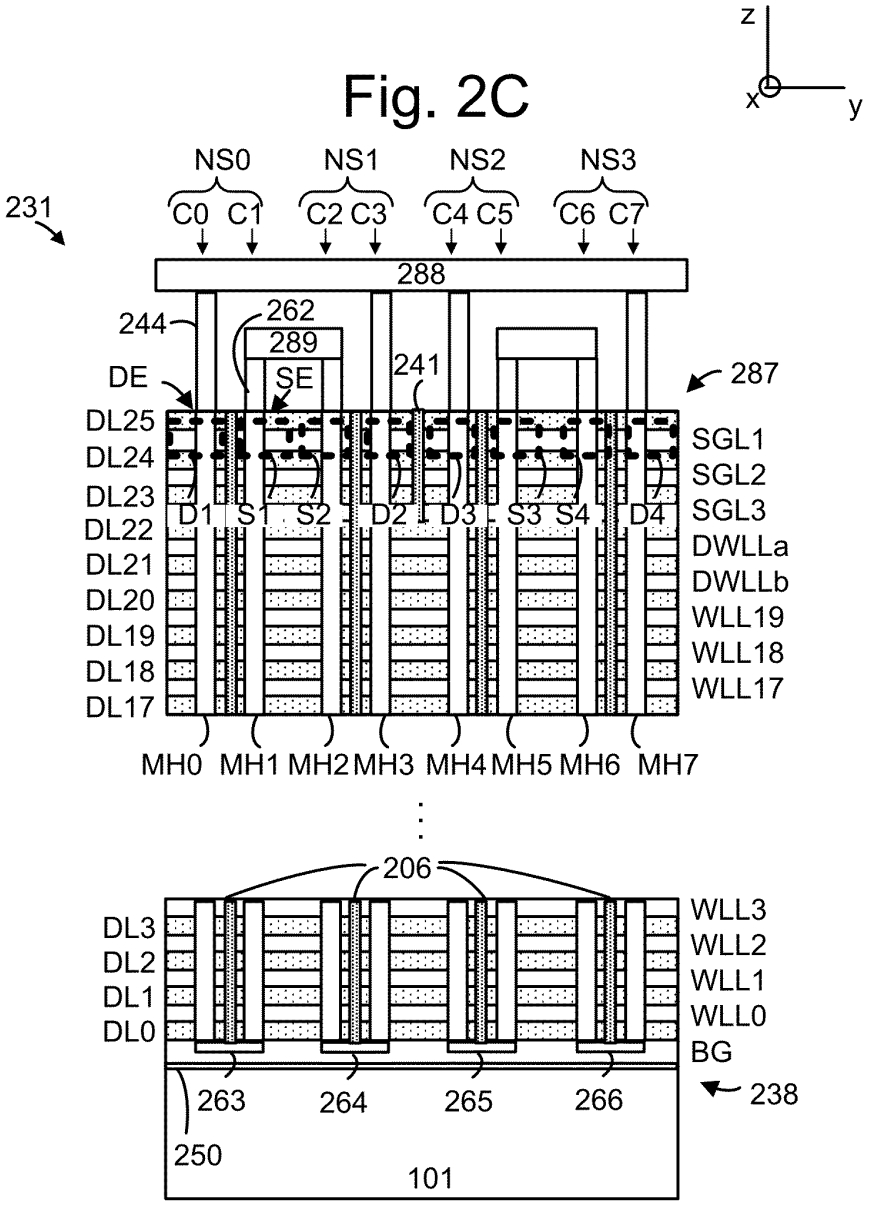
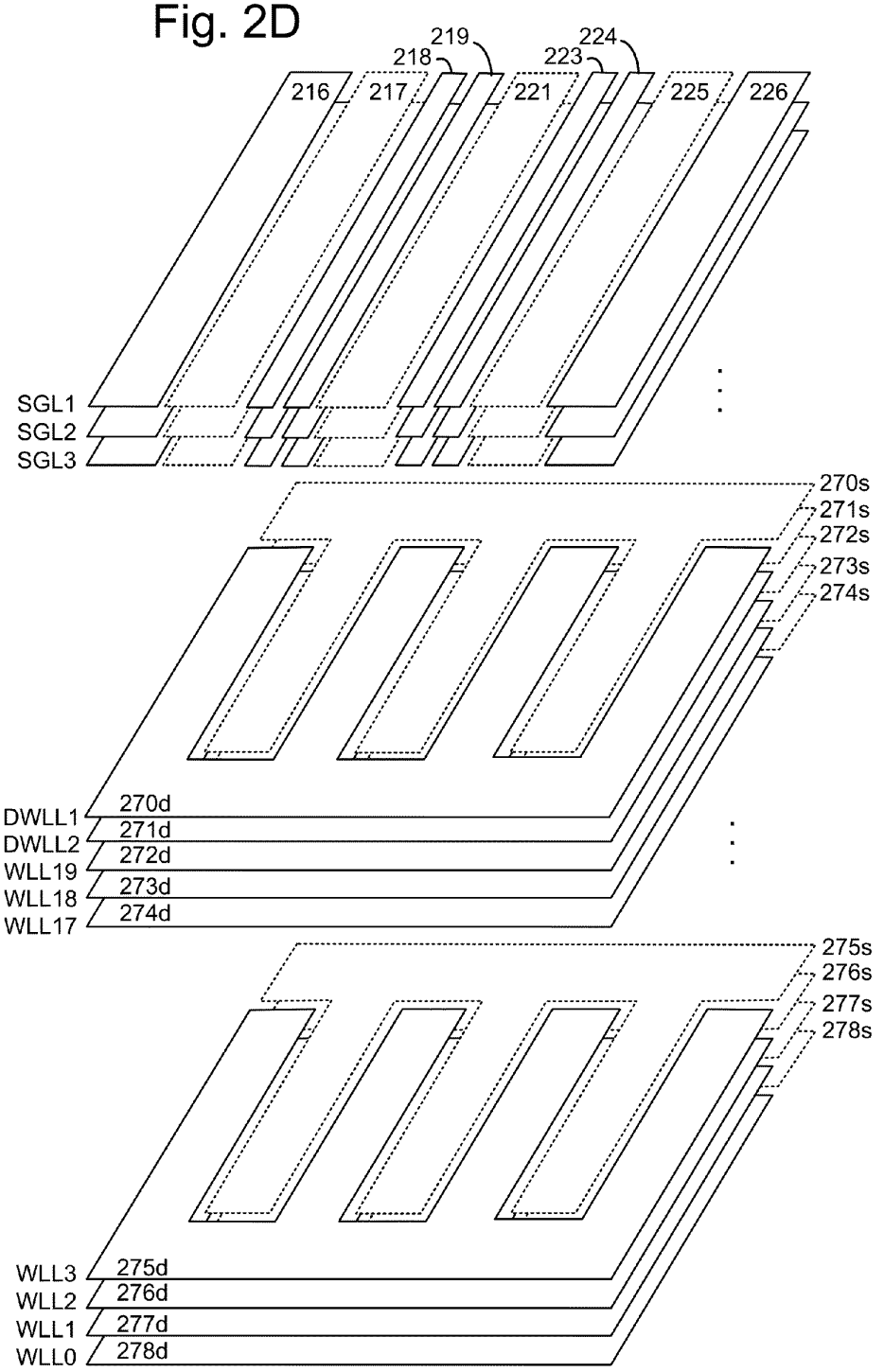

z
x
y
NS0
NS1
NS2
NS3
C0 C1
C2 C3
C4 C5
C6 C7
231
288
244
262
289
SE
241
287
DE
DL25
DL24
DL23
DL22
DL21
DL20
DL19
DL18
DL17
D1 S1 S2 D2 D3 S3 S4 D4
SGL1
SGL2
SGL3
DWLLa
DWLLb
WLL19
WLL18
WLL17
MH0 MH1 MH2 MH3 MH4 MH5 MH6 MH7
206
DL3
DL2
DL1
DL0
WLL3
WLL2
WLL1
WLL0
BG
263
264
265
266
238
250
101

Fig. 2D


219
224
218
223
216
217
221
225
226
SGL1
SGL2
SGL3
270s
271s
272s
273s
274s
DWLL1
DWLL2
WLL19
WLL18
WLL17
270d
271d
272d
273d
274d
275s
276s
277s
278s
WLL3
WLL2
WLL1
WLL0
275d
276d
277d
278d

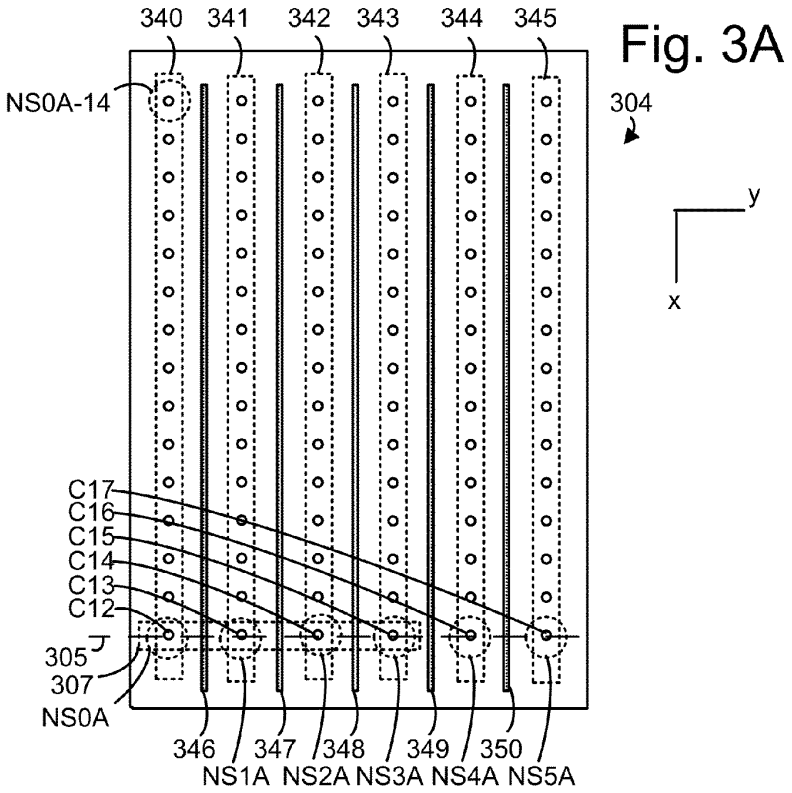

340
341
342
343
344
345
NS0A-14
304
y
x
C17
C16
C15
C14
C13
C12
305
307
NS0A
346
347
348
349
350
NS1A
NS2A
NS3A
NS4A
NS5A

Fig. 3A

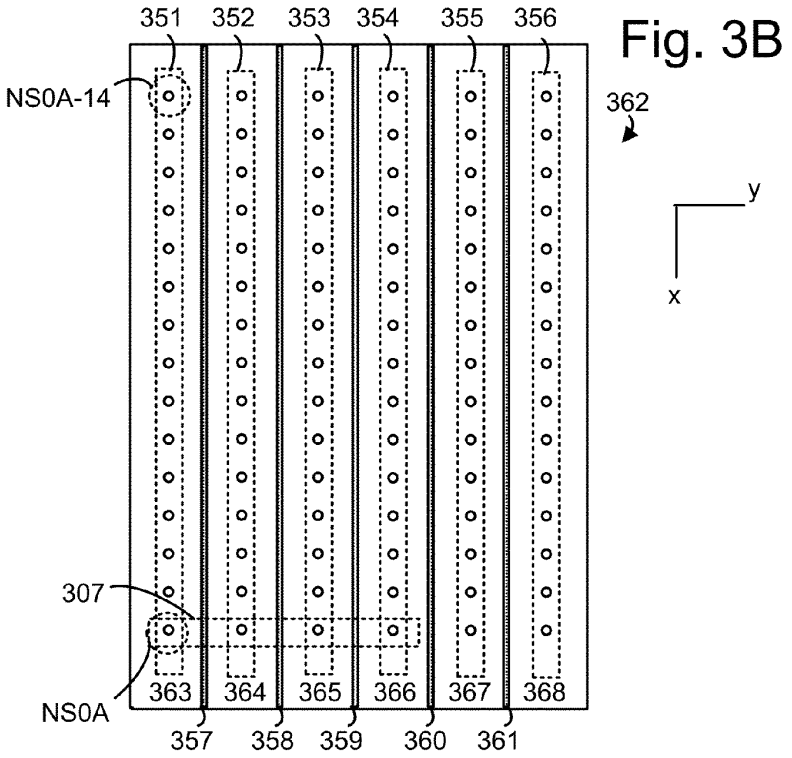

351
352
353
354
355
356
NS0A-14
362
y
x
307
NS0A
363
364
365
366
367
368
357
358
359
360
361

Fig. 3B

Fig. 3C1

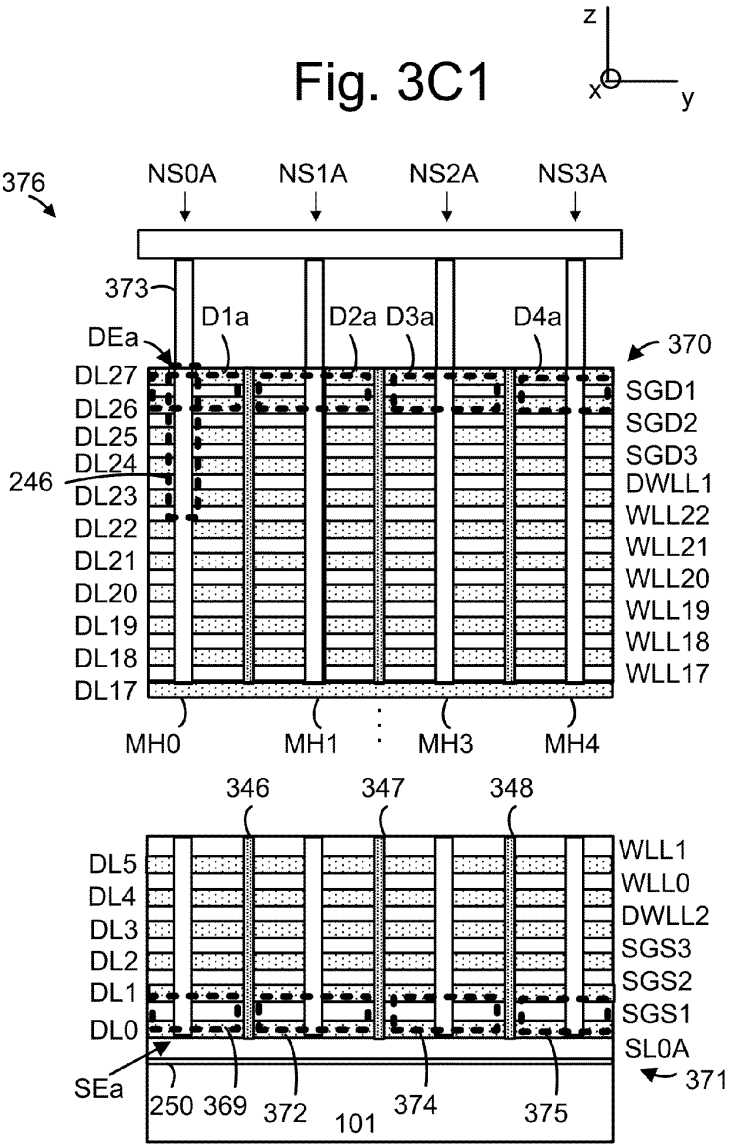


Fig. 3C2

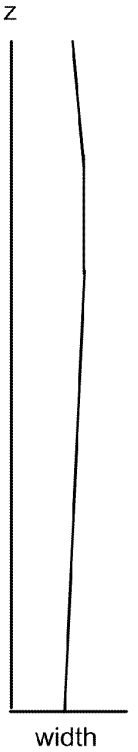
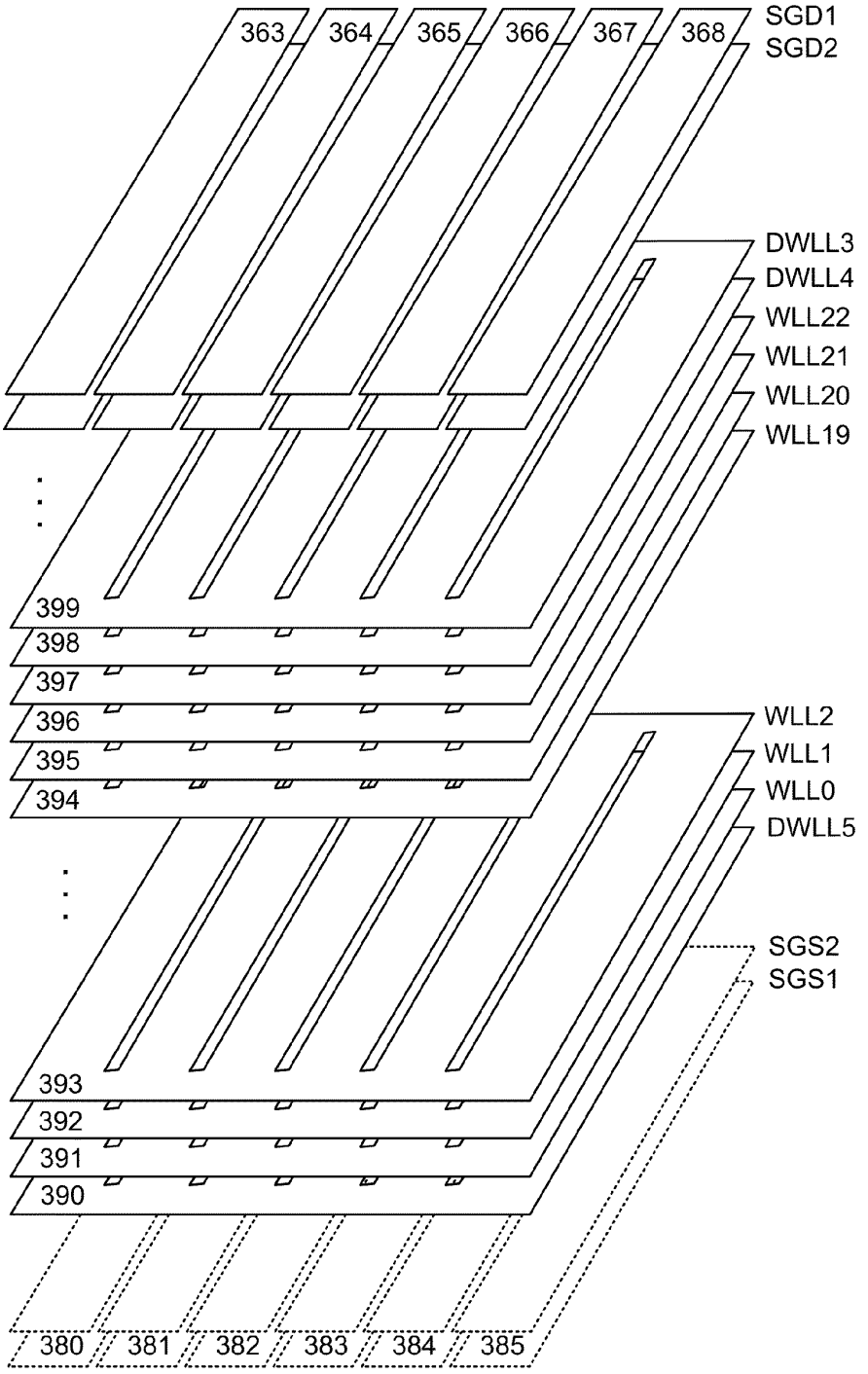


Fig. 3D


363
364
365
366
367
368
SGD1
SGD2
DWLL3
DWLL4
WLL22
WLL21
WLL20
WLL19
399
398
397
396
395
394
WLL2
WLL1
WLL0
DWLL5
SGS2
SGS1
393
392
391
390
380
381
382
383
384
385

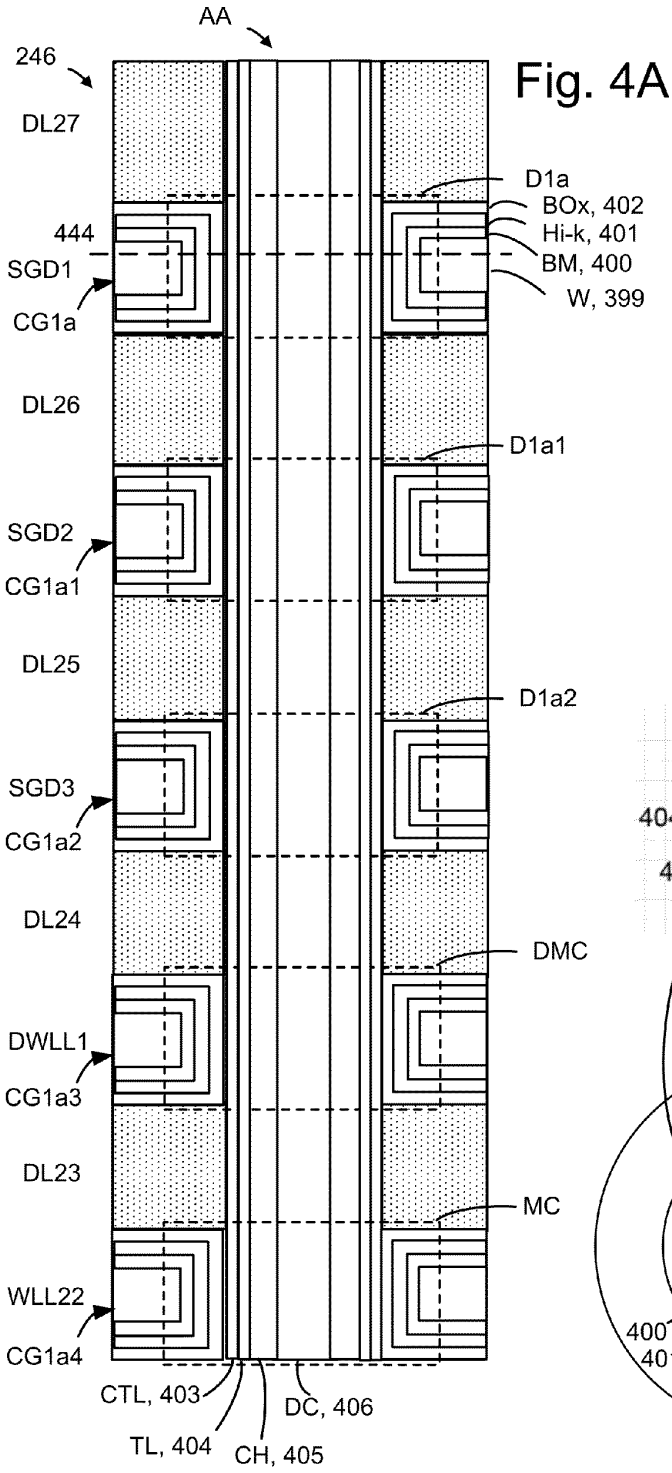


Fig. 4A

Fig. 4B2

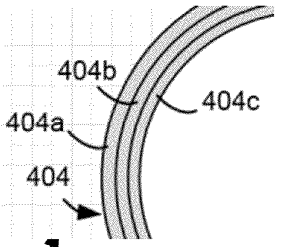
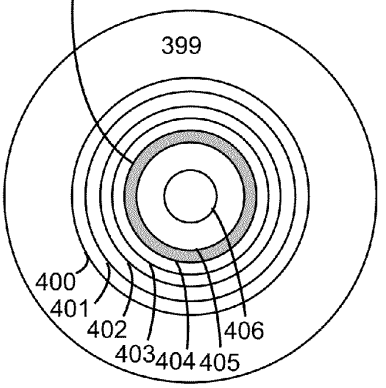


Fig. 4B1



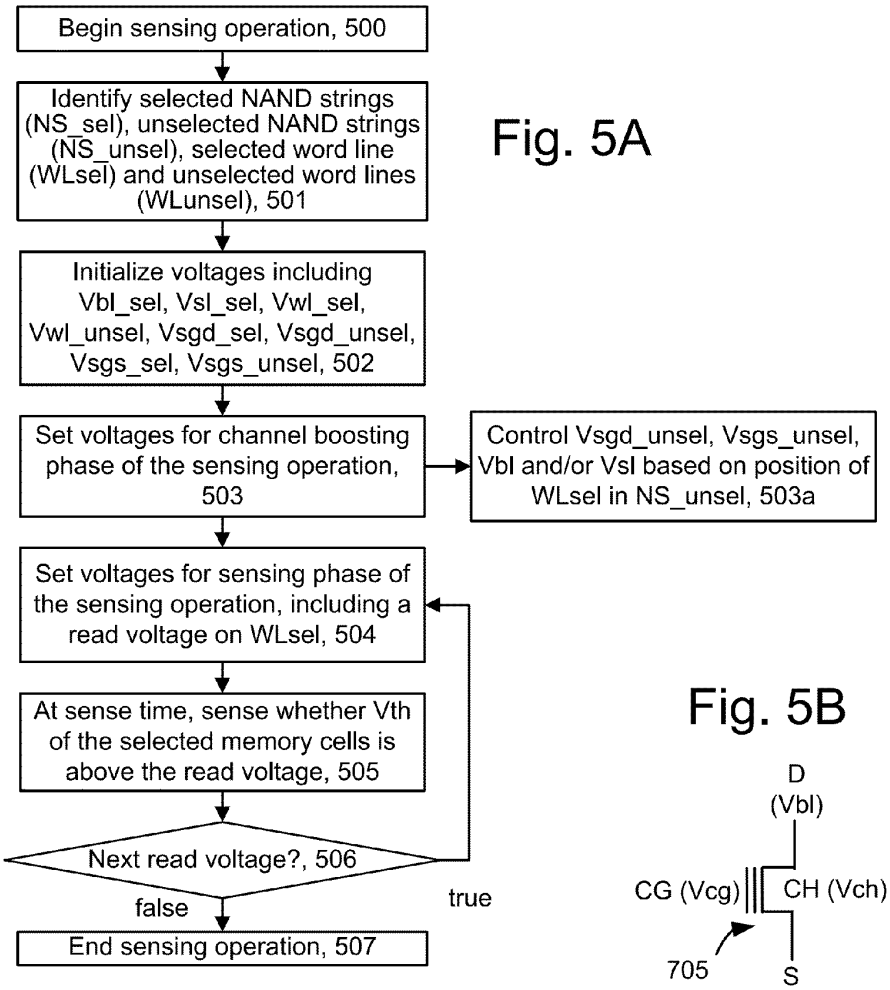


Fig. 5A

Fig. 5B

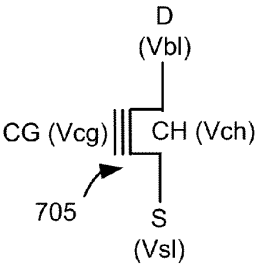


Fig. 6

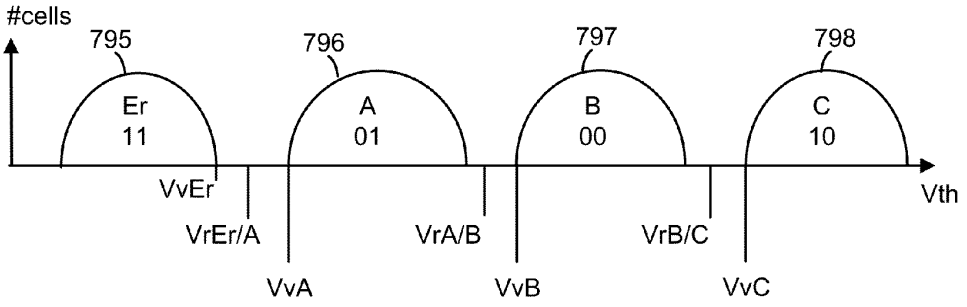


Fig. 7

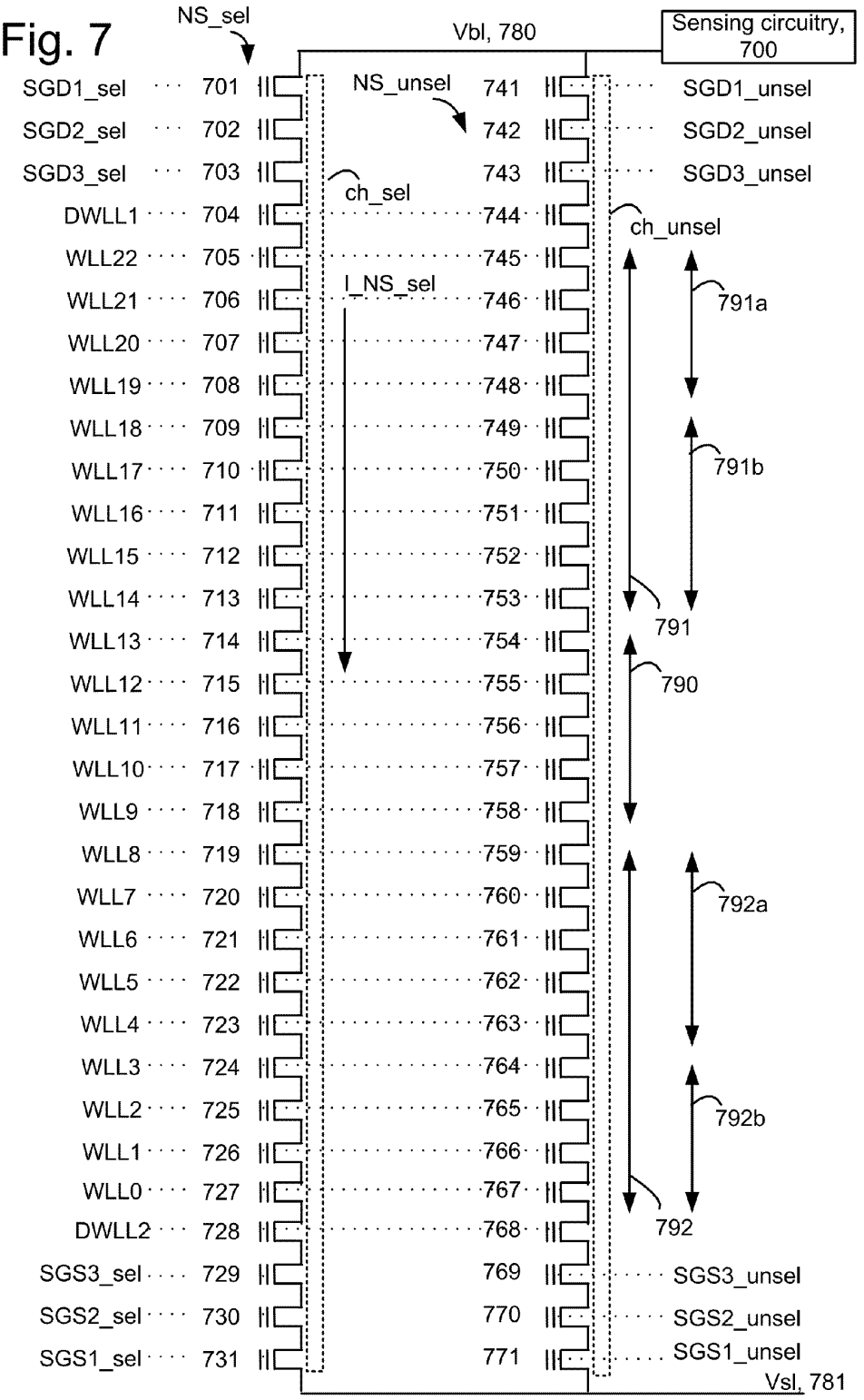

NS_sel
Vbl, 780
Sensing circuitry, 700
NS_unsel
SGD1_sel 701
SGD2_sel 702
SGD3_sel 703
DWLL1 704
WLL22 705
WLL21 706
WLL20 707
WLL19 708
WLL18 709
WLL17 710
WLL16 711
WLL15 712
WLL14 713
WLL13 714
WLL12 715
WLL11 716
WLL10 717
WLL9 718
WLL8 719
WLL7 720
WLL6 721
WLL5 722
WLL4 723
WLL3 724
WLL2 725
WLL1 726
WLL0 727
DWLL2 728
SGS3_sel 729
SGS2_sel 730
SGS1_sel 731
741
742
743
744
745
746
747
748
749
750
751
752
753
754
755
756
757
758
759
760
761
762
763
764
765
766
767
768
769
770
771
ch_sel
I_NS_sel
SGD1_unsel
SGD2_unsel
SGD3_unsel
ch_unsel
791a
791b
791
790
792a
792b
792
SGS3_unsel
SGS2_unsel
SGS1_unsel
Vsl, 781

Fig. 8A

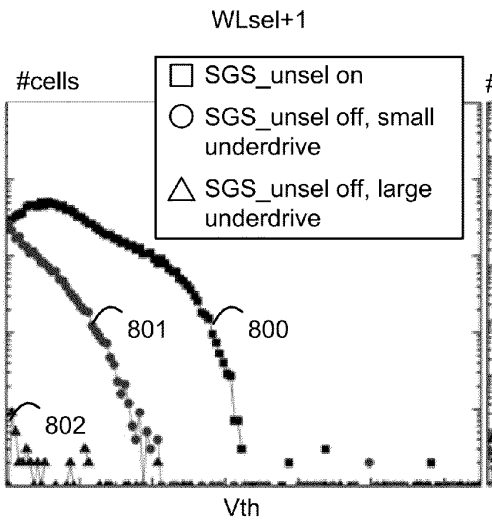


Fig. 8B

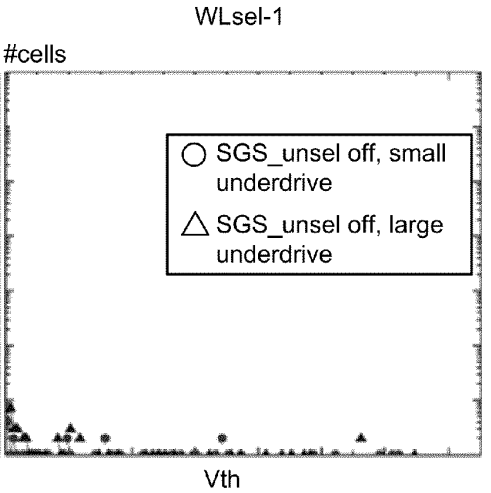


Fig. 10

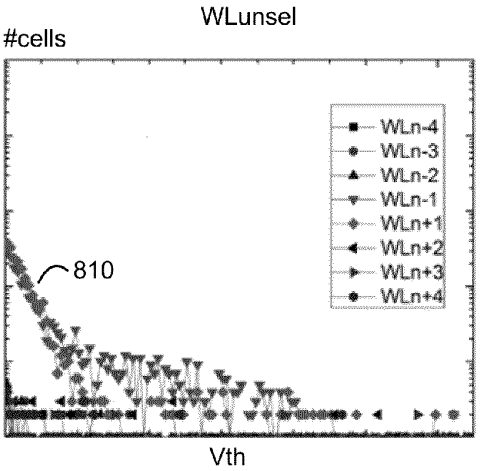


Fig. 9A

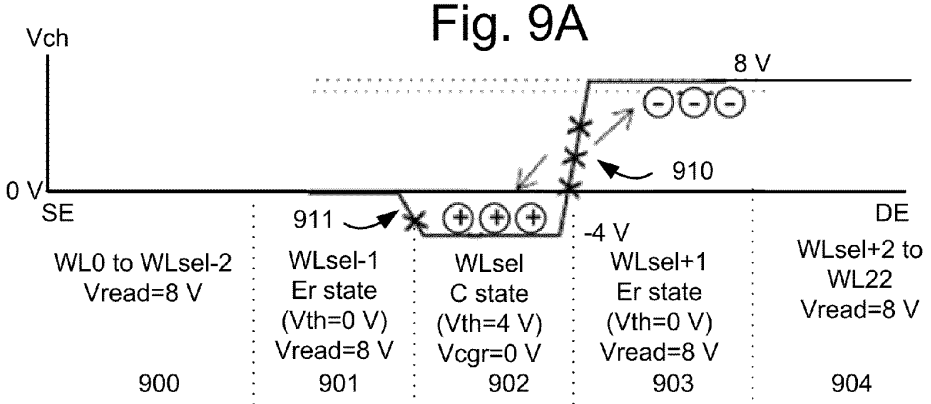


Fig. 9B

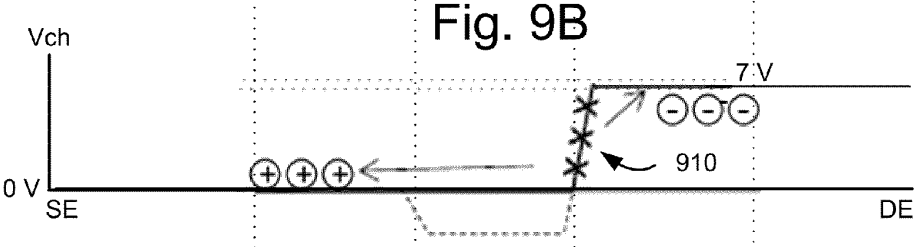


Fig. 9C

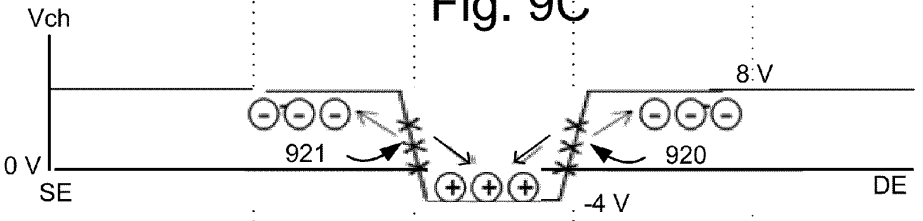


Fig. 9D

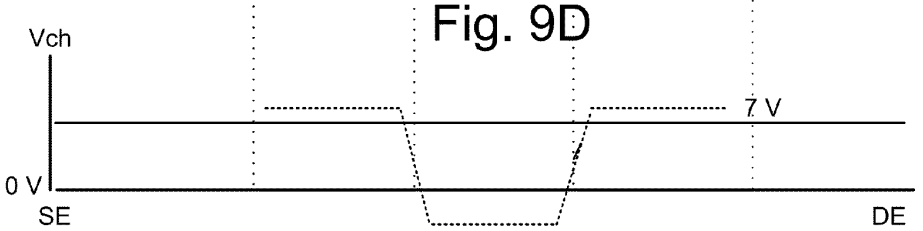


Fig. 11A

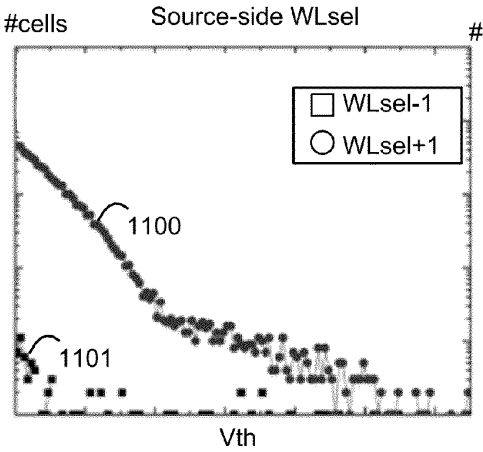
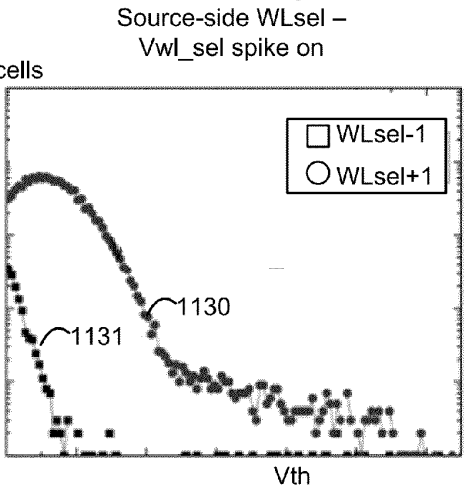


Fig. 11D



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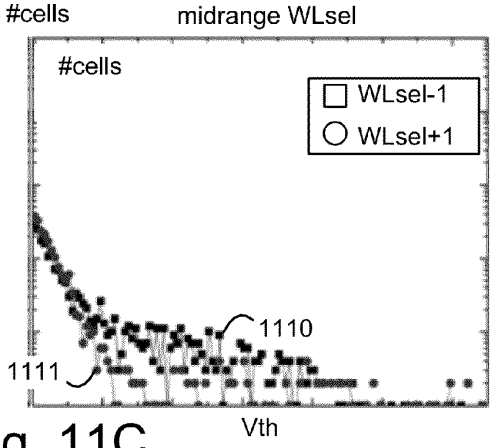
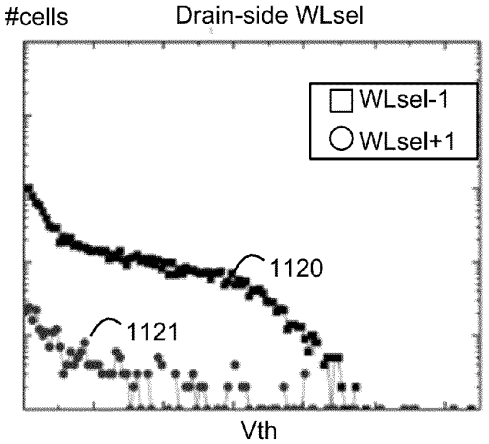


Fig. 11C



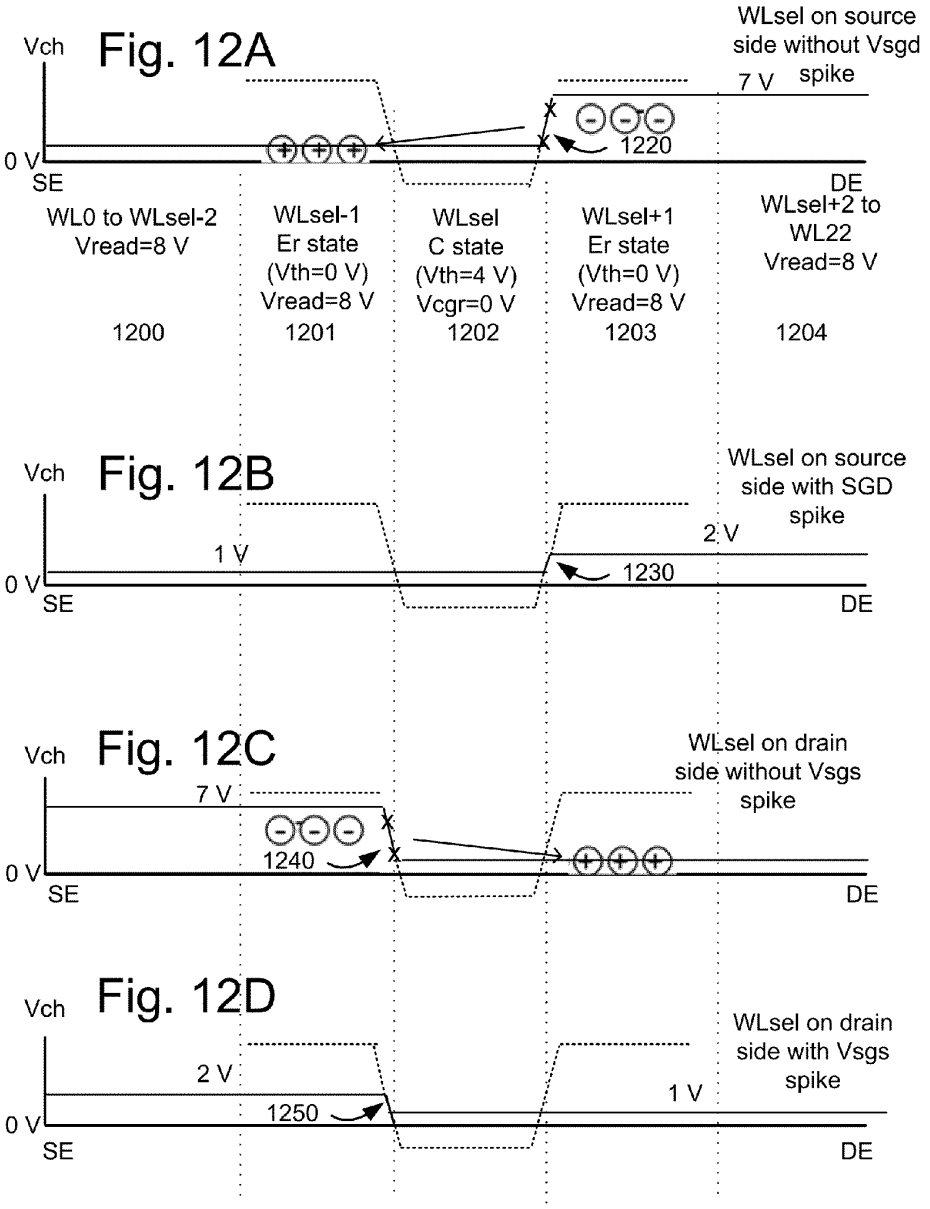


Fig. 12A
Vch
0 V
SE
DE
WLsel on source side without Vsgd spike
7 V
1220
WL0 to WLsel-2 Vread=8 V
1200
WLsel-1 Er state (Vth=0 V) Vread=8 V
1201
WLsel C state (Vth=4 V) Vcgr=0 V
1202
WLsel+1 Er state (Vth=0 V) Vread=8 V
1203
WLsel+2 to WL22 Vread=8 V
1204
Fig. 12B
Vch
0 V
SE
DE
WLsel on source side with SGD spike
1 V
2 V
1230
Fig. 12C
Vch
0 V
SE
DE
WLsel on drain side without Vsgs spike
7 V
1240
Fig. 12D
Vch
0 V
SE
DE
WLsel on drain side with Vsgs spike
2 V
1 V
1250

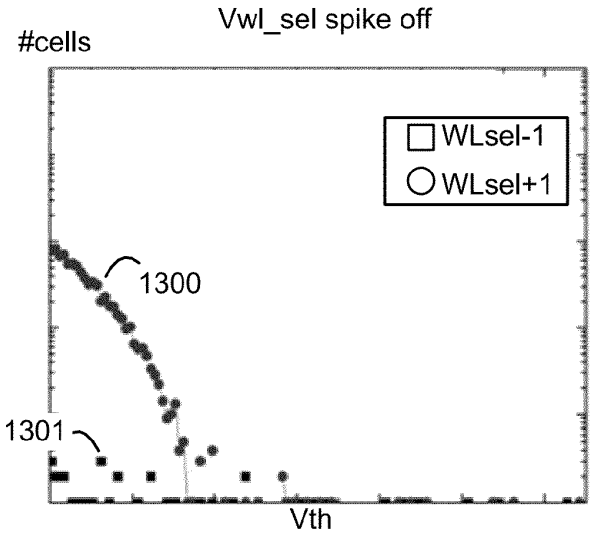


Fig. 13A

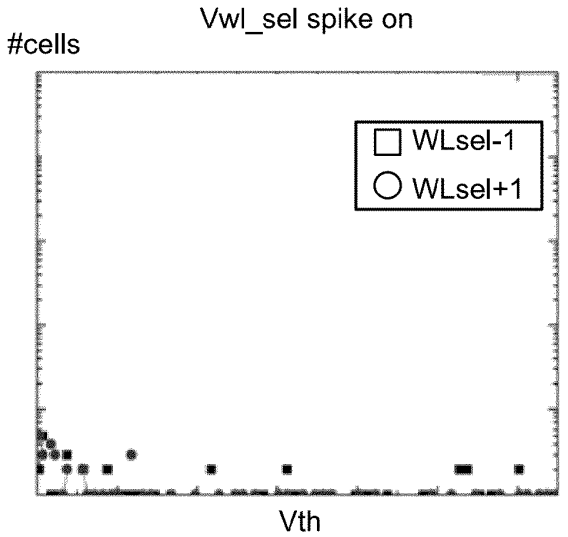


Fig. 13B

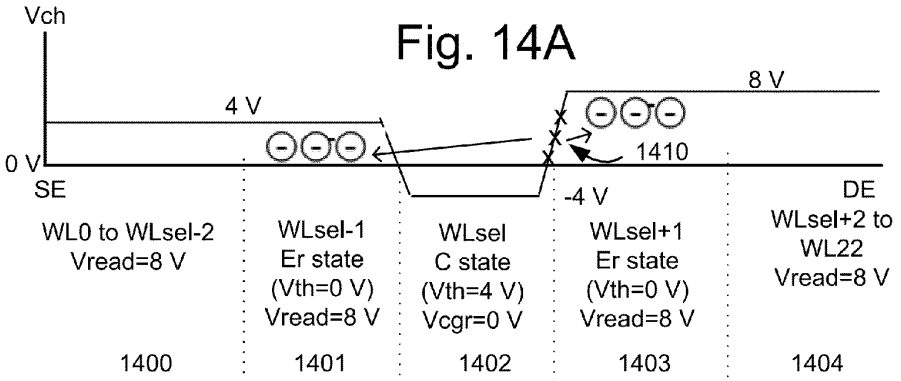


Fig. 14A
Vch
4 V
8 V
0 V
1410
-4 V
SE
DE
WL0 to WLsel-2
Vread=8 V
WLsel-1
Er state
(Vth=0 V)
Vread=8 V
WLsel
C state
(Vth=4 V)
Vcgr=0 V
WLsel+1
Er state
(Vth=0 V)
Vread=8 V
WLsel+2 to
WL22
Vread=8 V
1400
1401
1402
1403
1404

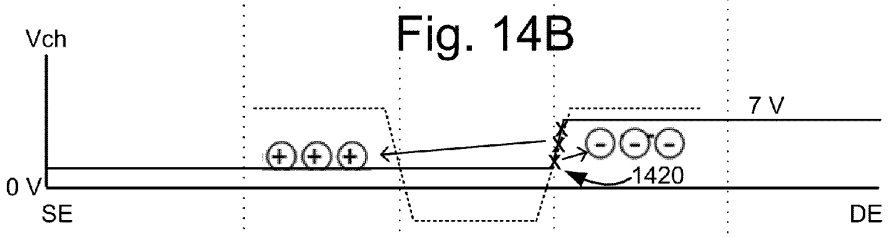


Fig. 14B
Vch
7 V
0 V
1420
SE
DE

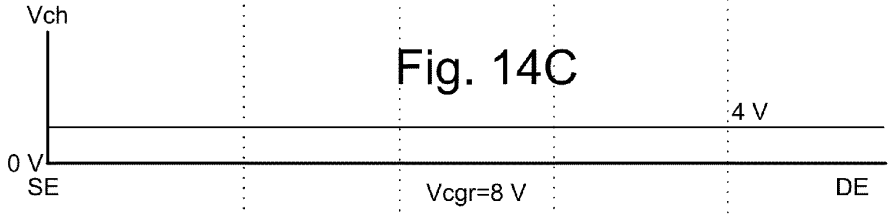


Fig. 14C
Vch
4 V
0 V
SE
Vcgr=8 V
DE

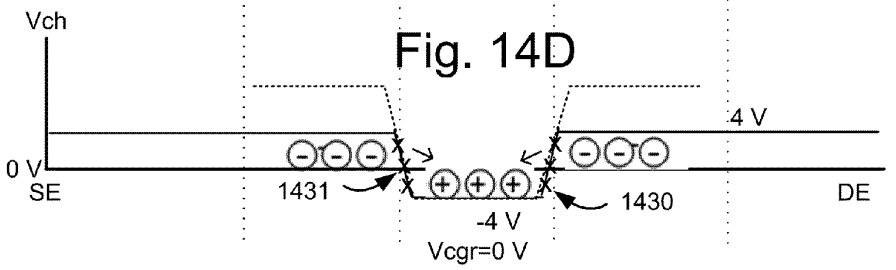


Fig. 14D
Vch
4 V
0 V
SE
1431
1430
DE
-4 V
Vcgr=0 V

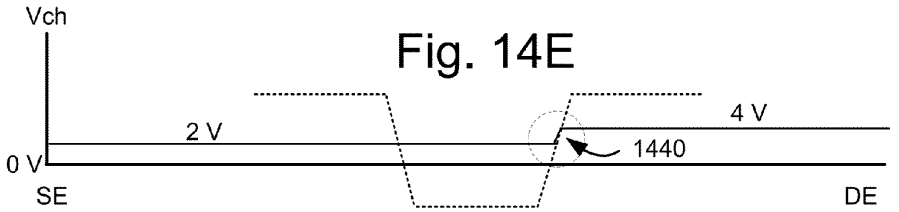


Fig. 14E
Vch
4 V
2 V
0 V
1440
SE
DE

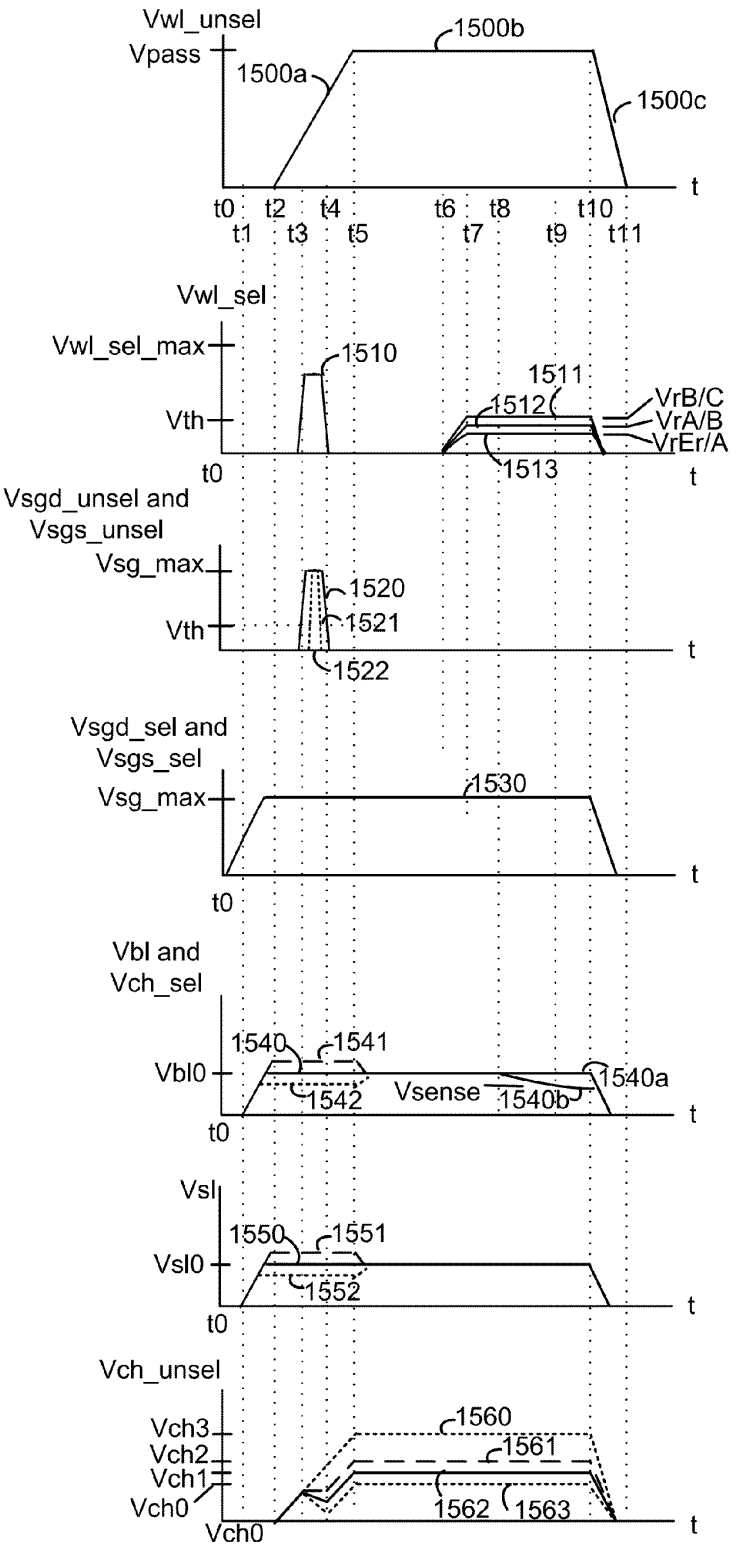


Fig. 15A

Fig. 15B

Fig. 15C

Fig. 15D

Fig. 15E

Fig. 15F

Fig. 15G

Fig. 16A

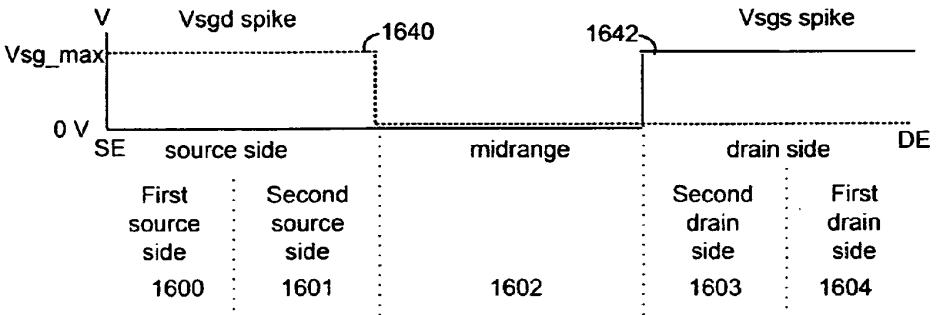


Fig. 16B

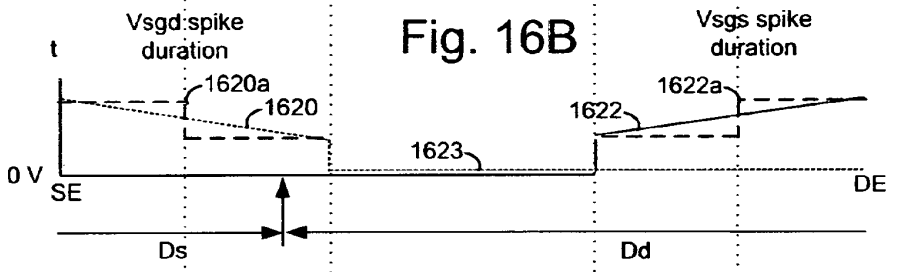
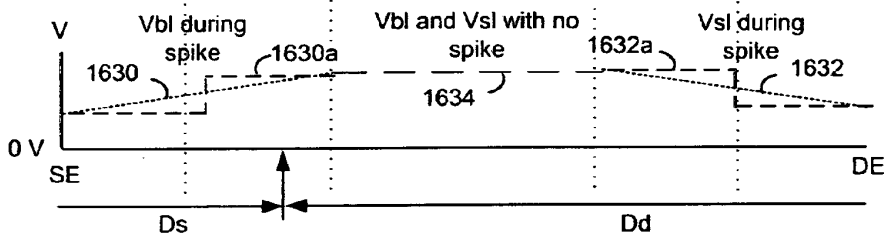


Fig. 16C



METHOD OF REDUCING HOT ELECTRON INJECTION TYPE OF READ DISTURB IN MEMORY

BACKGROUND

The present technology relates to operation of memory devices.

A charge-trapping material can be used in memory devices to store a charge which represents a data state. The charge-trapping material can be arranged vertically in a three-dimensional (3D) stacked memory structure, or horizontally in a two-dimensional (2D) memory structure. One example of a 3D memory structure is the Bit Cost Scalable (BiCS) architecture which comprises a stack of alternating conductive and dielectric layers. A memory hole is formed in the stack and a NAND string is then formed by filling the memory hole with materials including a charge-trapping layer. A straight NAND string extends in one memory hole, while a pipe- or U-shaped NAND string (P-BiCS) includes a pair of vertical columns of memory cells which extend in two memory holes and which are joined by a bottom back gate. Control gates of the memory cells are provided by the conductive layers.

However, various challenges are presented in operating such memory devices.

BRIEF DESCRIPTION OF THE DRAWINGS

Like-numbered elements refer to common components in the different figures.

FIG. **1**A is a perspective view of a 3D stacked non-volatile memory device.

FIG. **1**B is a functional block diagram of a memory device such as the 3D stacked non-volatile memory device **100** of FIG. **1**A.

FIG. **1**C depicts code which may be executed by a processor.

FIG. **1**D is a block diagram depicting one embodiment of the sense block SB**1** of FIG. **1**B.

FIG. **2**A depicts a top view of example word line layers **202** and **204** in a U-shaped NAND embodiment, as an example implementation of BLK**0** in FIG. **1**A.

FIG. **2**B depicts a top view of example select gate layer portions, consistent with FIG. **2**A.

FIG. **2**C depicts an embodiment of a stack **231** showing a cross-sectional view of the portion **209** of FIG. **2**A, along line **220**, where three select gate layers, SGL**1**, SGL**2** and SGL**3** are provided.

FIG. **2**D depicts an alternative view of the select gate layers and word line layers of the stack **231** of FIG. **2**C.

FIG. **3**A depicts a top view of an example word line layer **304** of the block BLK**0** of FIG. **1**A, in a straight NAND string embodiment.

FIG. **3**B depicts a top view of an example SGD layer **362**, consistent with FIG. **3**A.

FIG. **3**C**1** depicts an embodiment of a stack **376** showing a cross-sectional view of the portion **307** of FIG. **3**A, along line **305**, where three SGD layers, three SGS layers and dummy word line layers DWLL**1** and DWLL**2** are provided.

FIG. **3**C**2** depicts a variation in the width of a memory hole along its height.

FIG. **3**D depicts an alternative view of the select gate layers and word line layers of the stack **376** of FIG. **3**C.

FIG. **4**A depicts a view of the region **246** of FIG. **3**C**1**, showing SGD transistors D**1***a* (consistent with FIG. **3**C**1**), D**1***a***1** and D**1***a***2** above a dummy memory cell (DMC) and a data-storing memory cell (MC).

FIG. **4**B**1** depicts a cross-section view of the region **246** of FIG. **4**A along line **444**.

FIG. **4**B**2** depicts a close-up view of the tunneling layer **404** of FIG. **4**B**1**, showing an oxide **404***a*, nitride **404***b*, oxide **404***c* configuration.

FIG. **5**A depicts a process for performing a sensing operation on a selected word line, where a channel boosting voltage for an unselected NAND string is controlled based on a position of the selected word line (WLsel).

FIG. **5**B depicts a circuit diagram of an example memory cell such as the memory cell **705** of FIG. **7**.

FIG. **6** depicts a threshold voltage (Vth) distribution and example read voltages for a set of memory cells, consistent with the process of FIG. **5**A.

FIG. **7** depicts a circuit diagram of a selected NAND string (NS_sel) and an unselected NAND string (NS_unsel), consistent with the sensing process of FIG. **5**A and with the memory devices of FIGS. **2**C and **3**C**1**.

FIG. **8**A depicts a plot of a Vth distribution for memory cells of WLsel+1, including a plot **800** where the SGS transistor is conductive (on) and SGD is non-conductive (off), a plot **801** where the SGS and SGD transistors are non-conductive and the SGS transistor is underdriven by a smaller amount than the SGD transistor, and a plot **802** where the SGS and SGD transistors are non-conductive and the SGS transistor is underdriven by a same amount as the SGD transistor, where the amount of read stress is relatively small.

FIG. **8**B depicts a plot of a Vth distribution similar to FIG. **8**A except that it is for memory cells of WLsel−1.

FIG. **9**A depicts a plot of channel voltage (Vch) in an unselected NAND string, for a case where the SGS transistor is conductive and the SGD transistor is non-conductive, during the increase in Vpass.

FIG. **9**B depicts a plot of Vch in the unselected NAND string of FIG. **9**A in a next moment in time.

FIG. **9**C depicts a plot of Vch in an unselected NAND string, for a case where the SGS transistor and SGD transistor are non-conductive and are underdriven by a same amount, during the increase in Vpass.

FIG. **9**D depicts a plot of Vch in the unselected NAND string of FIG. **9**C, in a next moment in time.

FIG. **10** depicts a plot of a Vth distribution for memory cells of various unselected word lines near a selected word line, for a case where the SGS transistor and SGD transistor are non-conductive and are underdriven by a same amount, where the amount of read stress is relatively large.

FIG. **11**A depicts a plot of a Vth distribution for memory cells of WLsel+1 (**1101**) and WLsel−1 (**1100**), where the selected word line (WLsel) is source-side, the SGS transistor and SGD transistor are non-conductive and are underdriven by a same amount, and the amount of read stress is relatively large.

FIG. **11**B depicts a plot of a Vth distribution for memory cells of WLsel+1 (**1111**) and WLsel−1 (**1110**) under similar conditions as in FIG. **11**A except that WLsel is midrange.

FIG. **11**C depicts a plot of a Vth distribution for memory cells of WLsel+1 (**1121**) and WLsel−1 (**1120**) under similar conditions as in FIG. **11**A except that WLsel is drain-side.

FIG. **11**D depicts a plot of a Vth distribution for memory cells of WLsel+1 (**1130**) and WLsel−1 (**1131**), under similar conditions as in FIG. **11**A except that a spike is provided in Vwl_sel during the increase in Vpass.

FIG. **12**A depicts a plot of Vch in the unselected NAND string of FIG. **9**A, in a next moment in time, where WLsel is source-side and there is no spike in Vsgd_unsel.

FIG. **12**B depicts a plot of Vch in the unselected NAND string of FIG. **9**A, in a next moment in time, for a case where

the SGS transistor and SGD transistor are non-conductive and are underdriven by a same amount, except that a spike is provided in Vsgd_unsel during the increase in Vpass, and where WLsel is source-side.

FIG. **12**C depicts a plot of Vch in the unselected NAND string of FIG. **9**A, in a next moment in time, where WLsel is drain-side.

FIG. **12**D depicts a plot of Vch in the unselected NAND string of FIG. **9**A, in a next moment in time, for a case where the SGS transistor and SGD transistor are non-conductive and are underdriven by a same amount, except that a spike is provided in Vsgs during the increase in Vpass, and where WLsel is drain-side.

FIG. **13**A depicts a plot of a Vth distribution for memory cells of WLsel+1 (**1300**) and WLsel−1 (**1301**), where WLsel is midrange, the SGS and SGD transistors are non-conductive and the SGS transistor is underdriven by a smaller amount than the SGD transistor, a spike is not provided in Vwl_sel during the increase in Vpass, and the amount of read stress is relatively small.

FIG. **13**B depicts a plot of a Vth distribution for memory cells of WLsel+1 and WLsel−1 under similar conditions as in FIG. **13**A except that a spike is provided in Vwl_sel during the increase in Vpass.

FIG. **14**A depicts a plot of Vch in an unselected NAND string, for a case where the SGS and SGD transistors are non-conductive and the SGS transistor is underdriven by a smaller amount than the SGD transistor, during the increase in Vpass, where WLsel is midrange.

FIG. **14**B depicts a plot of Vch in the unselected NAND string of FIG. **14**A, in a next moment in time.

FIG. **14**C depicts a plot of Vch in an unselected NAND string under similar conditions as in FIG. **14**A except that a spike is provided in Vwl_sel during the increase in Vpass.

FIG. **14**D depicts a plot of Vch in the unselected NAND string of FIG. **14**C, at a first next moment in time.

FIG. **14**E depicts a plot of Vch in the unselected NAND string of FIG. **14**D, at a second next moment in time.

FIG. **15**A depicts an example waveform in a sensing operation for Vwl_unsel, the voltage on unselected word lines.

FIG. **15**B depicts an example waveform in a sensing operation for Vwl_sel, the voltage on the selected word line.

FIG. **15**C depicts an example waveform in a sensing operation for Vsgd_unsel, the voltage on an SGD transistor of an unselected NAND string, and Vsgs_unsel, the voltage on an SGS transistor of an unselected NAND string.

FIG. **15**D depicts an example waveform in a sensing operation for Vsgd_sel, the voltage on an SGD transistor of a selected NAND string, and Vsgs_sel, the voltage on an SGS transistor of a selected NAND string.

FIG. **15**E depicts an example waveform in a sensing operation for Vbl, the voltage on a bit line which is connected to selected and unselected NAND strings, and Vch_sel, the voltage in the channel of a selected NAND string.

FIG. **15**F depicts an example waveform in a sensing operation for Vsl, the voltage on a source line which is connected to selected and unselected NAND strings.

FIG. **15**G depicts an example waveform in a sensing operation for Vch_unsel, the voltage in the channel of an unselected NAND string.

FIG. **16**A depicts a plot showing a select gate voltage in a sensing operation as a function of a position of WLsel, where a Vsgd_unsel spike but no Vsgs_unsel spike is used if WLsel is source-side, no Vsgd or Vsgs_unsel spike is used if WLsel is midrange and a Vsgs_unsel spike but no Vsgd_unsel spike is used if WLsel is drain-side.

FIG. **16**B depicts a plot showing a spike duration (time t) of a select gate voltage in a sensing operation as a function of a position of WLsel, where a Vsgd_unsel spike is used having a variable duration but no Vsgs_unsel spike is used if WLsel is source-side, no Vsgd or Vsgs_unsel spike is used if WLsel is midrange and a Vsgs_unsel spike is used having a variable duration based, but no Vsgd_unsel spike is used if WLsel is drain-side.

FIG. **16**C depicts a plot showing a select gate voltage in a sensing operation as a function of a position of WLsel, where a Vsgd_unsel spike is used in which Vbl has a variable magnitude but no Vsgs_unsel spike is used if WLsel is source-side, no Vsgd or Vsgs_unsel spike is used if WLsel is midrange, and a Vsgs_unsel spike is used in which Vsl has a variable magnitude but no Vsgd_unsel spike is used if WLsel is drain-side.

DETAILED DESCRIPTION

Techniques are provided for performing a sensing operation in a memory device with reduced read disturb.

In an example, the memory device is a charge-trapping memory device. A charge-trapping memory device may use a charge-trapping material such as silicon nitride or other nitride, or in a multi-layer configuration such as an oxide-nitride-oxide (O—N—O) configuration. The charge-trapping material is separated from a channel layer by a tunneling layer. For example, a charge-trapping memory device may be a 3D memory device in which a stack of alternating conductive and dielectric layers are formed. Memory holes are etched in the stack and films are deposited in the holes such that memory cells or select gate transistors are formed where the conductive layers intersect with the memory holes. The films include a charge-trapping layer which extends vertically along an individual cell or an entire NAND string, a tunneling layer and a channel layer. Some of the conductive layers are used as control gates for memory cells and other conductive layers are used as control gates for select gate transistors, such as drain or source-side transistors in NAND strings. Another example of a charge-trapping memory device is a 2D memory device in which the charge-trapping layer extends horizontally along a NAND string.

In a 3D stacked non-volatile memory device, a read operation which is performed to read the state of selected memory cells can adversely impact the state of unselected memory cells in a process referred to a read disturb. For example, the memory device can be arranged in multiple blocks, where each block includes multiple sub-blocks, and a read operation is performed on a selected sub-block. The different sub-blocks can have the same word line layer, bit line and source line biases, but typically have separate select gate (SG) biases for source-side select gate (SGS) transistors and drain-side select gate (SGD) transistors. During the read in the selected sub-block, the SGS and SGD transistors of the unselected sub-blocks are typically turned off (made non-conductive) to cut off the conduction paths in unselected strings of the memory cells. A read-pass voltage (Vpass) of about 7-9 V is applied to the unselected word line layers, boosting a peak channel voltage of the unselected strings to about 8 V. This full measure of boosting is due to capacitive coupling from the unselected word line layers to the channel.

This channel boosting can help reduce the occurrence of normal read disturb for the unselected cells of the unselected strings. Normal read disturb results in an increase in the threshold voltage (Vth) of an unselected cell in a read operation. Normal read disturb is caused by weak Fowler-Nord-

heim (F-N) tunneling due to a large voltage difference between the control gate and a channel of a cell.

However, when a cell is being read with a relatively low voltage (Vwl_sel) on the selected word line layer, a large voltage gradient can be formed in the channel which results in electron/hole generation. This gradient can be formed between the selected word line and either of the adjacent word lines (e.g., WLsel+1 on the drain-side of WLsel and WLsel−1 on the source-side of WLsel). The generated electrons can be injected into the charge trap layers of the memory cells connected to the adjacent word lines and cause a hot electron injection (HEI) type of read disturb.

One way to suppress HEI read disturb is to discharge the boosting voltage inside the channel in the unselected NAND strings by grounding the channel, so that voltage gradient in the channel between the selected word line and the adjacent word lines is removed. However, this can result in an increase in the normal read disturb. Moreover, this approach does not account for the fact that the HEI read disturb is a function of the selected word line position and the amount of underdrive of the select gate transistors.

Techniques are provided herein in which the channel boosting voltage in unselected NAND strings is set to minimize read disturb including both normal read disturb and HEI read disturb. The techniques account for the position of the selected word line. In one approach, WLsel is at a source-side of the NAND strings. In this case, the SGD transistor of an unselected NAND string receives a voltage spike which provides the SGD transistor in a temporarily conductive state, during the ramping up of Vpass on the unselected word lines. This reduces the channel boosting voltage (Vch), in particular, on the drain-side of WLsel, since the channel is not capacitively coupled higher by Vpass while the SGD transistor is conductive. That is, the channel is not capacitively coupled higher because the channel is not floating during the spike. This approach reduces the channel gradient between WLsel and WLsel+1, so that HEI disturb is reduced for the memory cells in the unselected NAND strings which are connected to WLsel+1, where these memory cells are most susceptible to HEI disturb. Moreover, Vch on the drain-side of WLsel can be provided at a positive, non-zero level to minimize normal read disturb. Since the majority of the channel is on the drain-side of the selected word line, this portion of the channel will have an optimum Vch which minimizes read disturb.

In some cases, Vwl_sel is an edge word line at the source-side of the NAND strings. In other cases, Vwl_sel is a non-edge word line on the source-side of the NAND strings so that a remaining portion of the channel is on the source-side of WLsel. This portion of the channel may be cutoff from the portion of the channel on the drain-side of WLsel if Vwl_sel is sufficiently low compared to a Vth level of the associated memory cell. The source-side portion of the channel will tend to be capacitively coupled up to a relatively low level so that a spike on SGS is not used to reduce the associated Vch.

Alternatively, a spike in Vwl_sel can be used at the same time as the spike in the SGD transistor to allow the portion of the channel on the source-side of WLsel to communicate with the portion of the channel on the drain-side of WLsel. In this case, Vch on the source-side of WLsel will tend to be similar to Vch on the drain-side of WLsel.

Similarly, if WLsel is at a drain-side of the NAND strings, the SGS transistor of an unselected NAND string receives a voltage spike which provides the SGS transistor in a temporarily conductive state, during the ramping up of Vpass. This reduces the Vch on the source-side of WLsel. As a result, this approach reduces the channel gradient between WLsel and WLsel−1, so that HEI disturb is reduced for the memory cells in the unselected NAND strings which are connected to WLsel−1, where these memory cells are most susceptible to HEI disturb. Moreover, Vch on the source-side of WLsel can be provided at a positive, non-zero level to minimize normal read disturb.

If WLsel is in the middle of the NAND strings, the Vch may be balanced on either side of WLsel such that a significant channel gradient is not created between WLsel and WLsel−1, or between WLsel and WLsel+1, so that HEI disturb is avoided.

Additionally, the spike can be optimized according to the position of WLsel. For example, the spike on the SGD transistor can be longer in duration when WLsel is further from the SGD transistor, and the spike on the SGS transistor can be longer in duration when WLsel is further from the SGS transistor. Moreover, the bit line voltage (Vbl) spike can be lower in magnitude when WLsel is further from the SGD transistor, and higher in magnitude when WLsel is closer to the SGD transistor. In other words, a stronger countermeasure is taken to reduce HEI read disturb when the likelihood of the disturb is greater.

The following discussion provides details of the construction of example memory devices and of related techniques which address the above and other issues.

FIG. **1**A is a perspective view of a 3D stacked non-volatile memory device. The memory device **100** includes a substrate **101**. On the substrate are example blocks BLK**0** and BLK**1** of memory cells and a peripheral area **104** with circuitry for use by the blocks. The substrate **101** can also carry circuitry under the blocks, along with one or more lower metal layers which are patterned in conductive paths to carry signals of the circuitry. The blocks are formed in an intermediate region **102** of the memory device. In an upper region **103** of the memory device, one or more upper metal layers are patterned in conductive paths to carry signals of the circuitry. Each block comprises a stacked area of memory cells, where alternating levels of the stack represent word lines. In one possible approach, each block has opposing tiered sides from which vertical contacts extend upward to an upper metal layer to form connections to conductive paths. While two blocks are depicted as an example, additional blocks can be used, extending in the x- and/or y-directions.

In one possible approach, the length of the plane, in the x-direction, represents a direction in which signal paths to word lines extend in the one or more upper metal layers (a word line or SGD line direction), and the width of the plane, in the y-direction, represents a direction in which signal paths to bit lines extend in the one or more upper metal layers (a bit line direction). The z-direction represents a height of the memory device.

FIG. **1**B is a functional block diagram of a memory device such as the 3D stacked non-volatile memory device **100** of FIG. **1**A. The memory device **100** may include one or more memory die **108**. The memory die **108** includes a memory structure **126** of memory cells, such as an array of memory cells, control circuitry **110**, and read/write circuits **128**. In a 3D configuration, the memory structure can include the blocks BLK**0** and BLK**1** of FIG. **1**A. The memory structure **126** is addressable by word lines via a row decoder **124** and by bit lines via a column decoder **132**. The read/write circuits **128** include multiple sense blocks SB**1**, SB**2**, . . . , SBp (sensing circuitry) and allow a page of memory cells to be read or programmed in parallel. Typically a controller **122** is included in the same memory device **100** (e.g., a removable storage card) as the one or more memory die **108**. Commands and data are transferred between the host **140** and controller

122 via a data bus 120 and between the controller and the one or more memory die 108 via lines 118.

The memory structure can be 2D or 3D. The memory structure may comprise one or more array of memory cells including a 3D array. The memory structure may comprise a monolithic three dimensional memory structure in which multiple memory levels are formed above (and not in) a single substrate, such as a wafer, with no intervening substrates. The memory structure may comprise any type of non-volatile memory that is monolithically formed in one or more physical levels of arrays of memory cells having an active area disposed above a silicon substrate. The memory structure may be in a non-volatile memory device having circuitry associated with the operation of the memory cells, whether the associated circuitry is above or within the substrate.

The control circuitry 110 cooperates with the read/write circuits 128 to perform memory operations on the memory structure 126, and includes a state machine 112, an on-chip address decoder 114, and a power control module 116. The state machine 112 provides chip-level control of memory operations. A storage region 113 may be provided for parameters for a sensing operation as described herein.

The on-chip address decoder 114 provides an address interface between that used by the host or a memory controller to the hardware address used by the decoders 124 and 132. The power control module 116 controls the power and voltages supplied to the word lines and bit lines during memory operations. It can includes drivers for word line layers (WLLs) in a 3D configuration, SGS and SGD transistors and source lines. The sense blocks can include bit line drivers, in one approach. An SGS transistor is a select gate transistor at a source end of a NAND string, and an SGD transistor is a select gate transistor at a drain end of a NAND string.

In some implementations, some of the components can be combined. In various designs, one or more of the components (alone or in combination), other than memory structure 126, can be thought of as at least one control circuit which is configured to perform the actions described herein. For example, a control circuit may include any one of, or a combination of, control circuitry 110, state machine 112, decoders 114/132, power control module 116, sense blocks SB1, SB2, . . . , SBp (including the processor 192 and managing circuit MC0 in FIG. 1D), read/write circuits 128, and controller 122, and so forth. The sense block SB1 is discussed further in connection with FIG. 1D.

The off-chip controller 122 may comprise a processor 122*c* and storage devices (memory) such as ROM 122*a* and RAM 122*b*. The storage devices comprises code such as a set of instructions, and the processor is operable to execute the set of instructions to provide the functionality described herein. Alternatively or additionally, the processor can access code from a storage device 126*a* of the memory structure, such as a reserved area of memory cells in one or more word lines.

For example, FIG. 1C depicts code which may be executed by the processor 122*c*. The code 150 is used by the controller to access the memory structure such as for programming, read and erase operations. The code can include boot code 151 and control code (set of instructions) 160. The boot code is software that initializes the controller during a booting or startup process and enables the controller to access the memory structure. The code can be used by the controller to control one or more memory structures. Upon being powered up, the processor 122*c* fetches the boot code from the ROM 122*a* or storage device 126*a* for execution, and the boot code initializes the system components and loads the control code into the RAM 122*b*. Once the control code is loaded into the RAM, it is executed by the processor. The control code includes drivers to perform basic tasks such as controlling and allocating memory, prioritizing the processing of instructions, and controlling input and output ports.

The control code further includes instructions to apply an increasing voltage to unselected memory cells in unselected word lines of a memory device in connection with a sensing operation (161), instructions to control a select gate of an unselected NAND string to, at different times during the applying of the increasing voltage, allow a driven voltage on a bit line to reach a channel of the unselected NAND string and prevent the driven voltage on the bit line from reaching the channel of the unselected NAND string (162), and instructions to sense a current in the selected NAND string via the bit line while the boosting voltage is set in the channel of the unselected NAND string (163). Generally, the control code can include instructions to perform the functions described herein including the steps of the process of FIG. 5A.

Other types of non-volatile memory in addition to NAND flash memory can also be used.

Semiconductor memory devices include volatile memory devices, such as dynamic random access memory ("DRAM") or static random access memory ("SRAM") devices, non-volatile memory devices, such as resistive random access memory ("ReRAM"), electrically erasable programmable read only memory ("EEPROM"), flash memory (which can also be considered a subset of EEPROM), ferroelectric random access memory ("FRAM"), and magnetoresistive random access memory ("MRAM"), and other semiconductor elements capable of storing information. Each type of memory device may have different configurations. For example, flash memory devices may be configured in a NAND or a NOR configuration.

The memory devices can be formed from passive and/or active elements, in any combinations. By way of non-limiting example, passive semiconductor memory elements include ReRAM device elements, which in some embodiments include a resistivity switching storage element, such as an anti-fuse or phase change material, and optionally a steering element, such as a diode or transistor. Further by way of non-limiting example, active semiconductor memory elements include EEPROM and flash memory device elements, which in some embodiments include elements containing a charge storage region, such as a floating gate, conductive nanoparticles, or a charge storage dielectric material.

Multiple memory elements may be configured so that they are connected in series or so that each element is individually accessible. By way of non-limiting example, flash memory devices in a NAND configuration (NAND memory) typically contain memory elements connected in series. A NAND string is an example of a set of series-connected transistors comprising memory cells and select gate transistors.

A NAND memory array may be configured so that the array is composed of multiple strings of memory in which a string is composed of multiple memory elements sharing a single bit line and accessed as a group. Alternatively, memory elements may be configured so that each element is individually accessible, e.g., a NOR memory array. NAND and NOR memory configurations are exemplary, and memory elements may be otherwise configured.

The semiconductor memory elements located within and/or over a substrate may be arranged in two or three dimensions, such as a two dimensional memory structure or a three dimensional memory structure.

In a two dimensional memory structure, the semiconductor memory elements are arranged in a single plane or a single memory device level. Typically, in a two dimensional memory structure, memory elements are arranged in a plane

(e.g., in an x-y direction plane) which extends substantially parallel to a major surface of a substrate that supports the memory elements. The substrate may be a wafer over or in which the layer of the memory elements are formed or it may be a carrier substrate which is attached to the memory elements after they are formed. As a non-limiting example, the substrate may include a semiconductor such as silicon.

The memory elements may be arranged in the single memory device level in an ordered array, such as in a plurality of rows and/or columns. However, the memory elements may be arrayed in non-regular or non-orthogonal configurations. The memory elements may each have two or more electrodes or contact lines, such as bit lines and word lines.

A three dimensional memory array is arranged so that memory elements occupy multiple planes or multiple memory device levels, thereby forming a structure in three dimensions (i.e., in the x, y and z directions, where the z direction is substantially perpendicular and the x and y directions are substantially parallel to the major surface of the substrate).

As a non-limiting example, a three dimensional memory structure may be vertically arranged as a stack of multiple two dimensional memory device levels. As another non-limiting example, a three dimensional memory array may be arranged as multiple vertical columns (e.g., columns extending substantially perpendicular to the major surface of the substrate, i.e., in the y direction) with each column having multiple memory elements. The columns may be arranged in a two dimensional configuration, e.g., in an x-y plane, resulting in a three dimensional arrangement of memory elements with elements on multiple vertically stacked memory planes. Other configurations of memory elements in three dimensions can also constitute a three dimensional memory array.

By way of non-limiting example, in a three dimensional NAND memory array, the memory elements may be coupled together to form a NAND string within a single horizontal (e.g., x-y) memory device level. Alternatively, the memory elements may be coupled together to form a vertical NAND string that traverses across multiple horizontal memory device levels. Other three dimensional configurations can be envisioned wherein some NAND strings contain memory elements in a single memory level while other strings contain memory elements which span through multiple memory levels. Three dimensional memory arrays may also be designed in a NOR configuration and in a ReRAM configuration.

Typically, in a monolithic three dimensional memory array, one or more memory device levels are formed above a single substrate. Optionally, the monolithic three dimensional memory array may also have one or more memory layers at least partially within the single substrate. As a non-limiting example, the substrate may include a semiconductor such as silicon. In a monolithic three dimensional array, the layers constituting each memory device level of the array are typically formed on the layers of the underlying memory device levels of the array. However, layers of adjacent memory device levels of a monolithic three dimensional memory array may be shared or have intervening layers between memory device levels.

Then again, two dimensional arrays may be formed separately and then packaged together to form a non-monolithic memory device having multiple layers of memory. For example, non-monolithic stacked memories can be constructed by forming memory levels on separate substrates and then stacking the memory levels atop each other. The substrates may be thinned or removed from the memory device levels before stacking, but as the memory device levels are initially formed over separate substrates, the resulting memory arrays are not monolithic three dimensional memory arrays. Further, multiple two dimensional memory arrays or three dimensional memory arrays (monolithic or non-monolithic) may be formed on separate chips and then packaged together to form a stacked-chip memory device.

Associated circuitry is typically required for operation of the memory elements and for communication with the memory elements. As non-limiting examples, memory devices may have circuitry used for controlling and driving memory elements to accomplish functions such as programming and reading. This associated circuitry may be on the same substrate as the memory elements and/or on a separate substrate. For example, a controller for memory read-write operations may be located on a separate controller chip and/or on the same substrate as the memory elements.

One of skill in the art will recognize that this technology is not limited to the two dimensional and three dimensional exemplary structures described but covers all relevant memory structures within the spirit and scope of the technology as described herein and as understood by one of skill in the art.

FIG. **1**D is a block diagram depicting one embodiment of the sense block SB**1** of FIG. **1**B. The sense block is partitioned into one or more core portions, referred to as sense modules (e.g., SM**0**) or sense amplifiers, and a common portion, referred to as a managing circuit (e.g., MC**0**). In one embodiment, there is a separate sense module for each bit line and one common managing circuit for a set of sense modules, such as SM**0**, SM**1**, SM**2** and SM**3**. Each of the sense modules in a group communicates with the associated managing circuit via a data bus **172**. Thus, there are one or more managing circuits which communicate with the sense modules of a set of memory cells.

Each sense module SM**0**, SM**1**, SM**2** and SM**3** comprises sense circuitry SC**0**, SC**1**, SC**2** and SC**3**, respectively, that performs sensing by determining whether a conduction current in a connected bit line BL**0**, BL**1**, BL**2** and BL**3**, respectively, is above or below a predetermined threshold voltage (verify voltage). Each sense module SM**0**, SM**1**, SM**2** and SM**3** also includes a bit line latch BLL**0**, BLL**1**, BLL**2** and BLL**3**, respectively, that is used to set a voltage condition on the connected bit line. For example, during a programming voltage, a predetermined state latched in a bit line latch will result in the connected bit line being pulled to a lockout state (e.g., 1.5-3 V), a slow programming state (e.g., 0.5-1 V) or a normal programming state (e.g., 0 V).

Managing circuit MC**0** comprises a processor **192**, four example sets of data latches **194**, **195**, **196** and **197** and an I/O interface **198** coupled between the sets of data latches and the data bus **120**. One set of data latches can be provide for each sense module, and may include data latches identified by LDL and UDL. LDL stores a bit for a lower page (LP) of write data, and UDL stores a bit for an upper page (UP) of write data, in a memory which stores two bits of data in each memory cell.

Additional data latches could be used as well. For example, in a three-bit per memory cell implementation, one extra data latch may be used to store a middle page (MP) of data. A four-bit per memory cell implementation can use lower-middle and upper-middle data latches. The techniques provided herein are meant to encompass such variations. In a further option, another latch is used to identify whether a memory cell is in a slow programming mode when its Vth is within a specified margin of the verify voltage of its target data state.

The processor **192** performs computations during reading and programming. For reading, the processor determines the

data state stored in the sensed memory cell and stores the data in the set of data latches. For full programming and refresh programming, the processor reads the latches to determine the data state which is to be written to a memory cell.

During reading, the operation of the system is under the control of the state machine **112** which controls the supply of different control gate voltages to the addressed memory cell. As it steps through the various predefined control gate voltages (e.g., VrEr/A, VrA/B and VrB/C in FIG. **6**) corresponding to the various memory states supported by the memory (e.g., states A, B and C), the sense module may trip at one of these voltages and a corresponding output will be provided from the sense module to the processor **192** via the data bus **172**. At that point, processor **192** determines the memory state by consideration of the tripping event(s) of the sense module and the information about the applied control gate voltage from the state machine via input lines **193**. It then computes a binary encoding for the memory state and stores the resultant data bits into the sets of data latches **194-197**. In another embodiment of the managing circuit MC**0**, the bit line latch serves both as a latch for latching the output of the sense module and also as a bit line latch as described above.

Some implementations can include multiple processors. In one embodiment, each processor will include an output line (not depicted) such that each of the output lines is wired-OR'd together. In some embodiments, the output lines are inverted prior to being connected to the wired-OR line. This configuration enables a quick determination during the program verification process of when the programming process has completed because the state machine receiving the wired-OR can determine when all bits being programmed have reached the desired level. For example, when each bit has reached its desired level, a logic zero for that bit will be sent to the wired-OR line (or a data one is inverted). When all bits output a data 0 (or a data one inverted), then the state machine knows to terminate the programming process. Because each processor communicates with four sense modules, the state machine needs to read the wired-OR line four times, or logic is added to processor **192** to accumulate the results of the associated bit lines such that the state machine need only read the wired-OR line one time. Similarly, by choosing the logic levels correctly, the global state machine can detect when the first bit changes its state and change the algorithms accordingly.

During program or verify operations, the data to be programmed (write data) is stored in the set of data latches **194-197** from the data bus **120**, in the LP and UP data latches. The programming operation, under the control of the state machine, comprises a series of programming voltage pulses applied to the control gates of the addressed memory cells. Each programming voltage is followed by a read back (verify) to determine if the memory cell has been programmed to the desired memory state. In some cases, processor monitors the read back memory state relative to the desired memory state. When the two states agree, the processor sets the bit line latch to cause the bit line to be pulled to a state designating program inhibit (e.g., 2-3 V). This inhibits the memory cell coupled to the bit line from further programming even if programming voltages appear on its control gate. In other embodiments, the processor initially loads the bit line latch and the sense circuitry sets it to an inhibit value during the verify process.

Each set of data latches **194-197** may be implemented as a stack of data latches for each sense module. In one embodiment, there are three data latches per sense module. In some implementations, the data latches are implemented as a shift register so that the parallel data stored therein is converted to serial data for data bus **120**, and vice versa. All the data latches corresponding to the read/write block of memory cells can be linked together to form a block shift register so that a block of data can be input or output by serial transfer. In particular, the bank of read/write modules is adapted so that each of its set of data latches will shift data in to or out of the data bus in sequence as if they are part of a shift register for the entire read/write block.

FIG. **2**A depicts a top view of example word line layers **202** and **204** in a U-shaped NAND embodiment, as an example implementation of BLK**0** in FIG. **1**A. In a 3D stacked memory device, memory cells are formed along memory holes which extend through alternating conductive and dielectric layers in a stack. The memory cells are typically arranged in NAND strings. Each conductive layer can include one or more word line layers. A word line layer is an example of a word line.

The view is of a representative layer among the multiple WLLs in a stack. Referring also to FIG. **2**C, the stack includes alternating dielectric and conductive layers. The dielectric layers include DL**0** to DL**25** and may be made of SiO_2, for instance. The conductive layers include a back gate layer (BGL), data-storing word line layers WLL**0** to WLL**19**, dummy (non-data-storing) word line layers DWLLa and DWLLb, and select gate layers SGL**1**, SGL**2** and SGL**3**. The word line layers are conductive paths to control gates of the memory cells at the layer. Moreover, each select gate layer may comprises conductive lines to select gate transistors (e.g., SGD and/or SGS transistors).

The word line layers of FIG. **2**A may represent any one of the word line layers in FIG. **2**C. These conductive layers may include doped polysilicon, metal such as tungsten or metal silicide, for instance. An example voltage of 5-10 V may be applied to the back gate to maintain a conductive state which connects the drain- and source-side columns.

For each block, each conductive layer may be divided into two word line layers **202** and **204** which are insulated from one another by a slit **206**. The slit is formed by etching a void which extends vertically in the stack, typically from an etch stop layer at the bottom to at least a top layer of the stack, then filling the slit with insulation. This is an example of the type of etching which can result in the accumulation of charges in the top conductive layer of the stack. The slit **206** is a single continuous slit which extends in a zig-zag pattern in the block. This approach can provide greater flexibility in controlling the memory cells since the WLLs can be driven independently.

Each block includes vertically-extending memory holes or pillars which extend vertically in the stack, and comprise a column of memory cells such as in a NAND string. Each circle represents a memory hole or a memory cell associated with the word line layer. Example columns of memory cells along a line **220** include C**0** to C**11**. Columns C**0**, C**3**, C**4**, C**7**, C**8** and C**11** represent the drain-side columns of respective NAND strings. Columns C**1**, C**2**, C**5**, C**6**, C**9** and C**10** represent the source-side columns of respective NAND strings. The figure represents a simplification, as many more rows of memory holes will typically be used, extending to the right and left in the figure. Also, the figures are not necessarily to scale. The columns of memory cells can be arranged in subsets such as sub-blocks.

Further, the NAND strings are arranged in sets, where each NAND string in a set has an SGD transistor with a common control gate voltage. See also FIG. **2**A. Regions **201**, **203**, **205**, **207**, **208** and **210** each represent a set of NAND strings, or a set of memory cells in a word line layer. For example, region **210** includes NAND strings NS**0**, . . . , NS**0-14**. A programming operation can involve one set of NAND strings.

Each NAND string in a set can be associated with a respective bit line which is independently controlled to allow or inhibit programming.

The drawings are not to scale and do not show all memory columns. For example, a more realistic block might have twelve memory columns in the y direction as shown, but a very large number such as 32 k memory columns in the x direction, for a total of 384,000 memory columns in a block. With U-shaped NAND strings, 192 k NAND strings are provided in this example. With straight NAND strings, 384,000 NAND strings are provided in this example. Assuming there are twenty-four memory cells per column, there are 384,000×24=9,216,000 memory cells in the set.

FIG. **2**B depicts a top view of example select gate layer portions, consistent with FIG. **2**A. In one approach, the select gate layer **215** is different than a WLL in that a separate SGD layer portion or line, is provided for each set of NAND strings. That is, each single row of SGD transistors extending in the x direction is separately controlled. In other words, the control gates of the SGD transistors in each set of NAND strings are commonly controlled.

Further, an SGS layer portion or line is provided for a pair of rows of SGS transistors extending in the x direction, in one approach, for adjacent sets of NAND strings. Optionally, additional slits are used so that a separate SGS layer portion is provided for a single row of SGS transistors extending in the x direction. Thus, the control gates of the SGS transistors in a pair of rows of SGS transistors, or in a single row of SGS transistors, are also commonly controlled.

The SGS and SGD layer portions are created due to slits **239**, **240**, **241**, **242**, **243**, **245**, **247** and **248**. The slits extend partway down in the stack as depicted by example slit **241** in FIG. **2**C. Regions **227**, **228**, **229**, **232**, **233** and **237** represent SGD transistors in SGD lines **216**, **218**, **219**, **223**, **224** and **226**, respectively. Regions **253** and **254**, **255** and **257**, and **258** and **259** represent SGS transistors in SGS lines **217**, **221** and **225**, respectively. Regions **255** and **257**, **258** and **259**, represent SGS transistors in SGS layer portions **221** and **225**, respectively. The portion **209** from FIG. **2**A is repeated for reference.

The select gate transistors are associated with NAND strings NS**0**-NS**5**.

FIG. **2**C depicts an embodiment of a stack **231** showing a cross-sectional view of the portion **209** of FIG. **2**A, along line **220**, where three select gate layers, SGL**1**, SGL**2** and SGL**3** are provided. In this case, the slit extends down to DL**22**, so that three separate layers of select gate transistors are formed in each column of each NAND string. The stack has a top **287** and a bottom **238**.

The conductive layers of the select gates can have a same height (channel length) as the conductive layers of the memory cells, in one approach. This facilitates the fabrication of the memory device. In a column, the individual select gate transistors together are equivalent to one select gate transistor having a channel length which is the sum of the channel lengths of the individual select gate transistors. Further, in one approach, select gate transistors in a column (e.g., in layers SGL**1**, SGL**2** and SGL**3**) are connected and received a common voltage during operations. The SGS transistors can have a similar construction as the SGD transistors. Further, the SGS and SGD transistors can have a similar construction as the memory cell transistors.

The substrate may be p-type and can provide a ground which is connected to the top select gate layer, in one approach. A via **244** connects a drain-side of C**0** and NS**0** to a bit line **288**. A via **262** connects a source-side of C**1** and NS**0** to a source line **289**. Back gates **263**, **264**, **265** and **266** are provided in NS**0**, NS**1**, NS**2** and NS**3**, respectively.

Regions D**1**, D**2**, D**3** and D**4** represent SGD transistors and regions S**1**, S**2**, S**3** and S**4** represent SGS transistors in SGL**1**.

FIG. **2**D depicts an alternative view of the select gate layers and word line layers of the stack **231** of FIG. **2**C. The SGL layers SGL**1**, SGL**2** and SGL**3** each includes parallel rows of select gate lines associated with the drain-side (shown by solid lines) or source-side (shown by dotted lines) of a set of NAND strings. For example, SGL**1** includes drain-side select gate lines **216**, **218**, **219**, **223**, **224** and **226** and source-side select gate lines **217**, **221** and **225**, consistent with FIG. **2**B. Each select gate line can be independently controlled, in one approach.

Below, the SGL layers are the word line layers. Each word line layer includes a drain-side word line connected to memory cells on a drain-side of a NAND string (the half of a NAND string between the back gate and the drain end) and a source-side word line connected to memory cells on a source-side of a NAND string (the half of a NAND string between the back gate and the source end). For example, DWLL**1**, DWLL**2**, WLL**19**, WLL**18** and WLL**17** include drain-side word lines **270***d*, **271***d*, **272***d*, **273***d* and **274***d*, respectively, and source-side word lines **270***s*, **271***s*, **272***s*, **273***s* and **274***s*, respectively.

WLL**3**, WLL**2**, WLL**1** and WLL**0** include drain-side word lines **275***d*, **276***d*, **277***d* and **278***d*, respectively, and source-side word lines **275***s*, **276***s*, **277***s* and **278***s*, respectively. Each word line can be controlled independently, in one approach.

In an example programming operation, the source-side word line **272***s* is a first programmed word line and a drain-side word line **272***d* is a final programmed word line in a block.

FIG. **3**A depicts a top view of an example word line layer **304** of the block BLK**0** of FIG. **1**A, in a straight NAND string embodiment. In this configuration, a NAND string has only one column, and the source-side select gate is on the bottom of the column instead of on the top, as in a U-shaped NAND string. Moreover, a given level of a block has one WLL which is connected to each of the memory cells of the layer. Insulation-filled slits **346**, **347**, **348**, **349** and **350** can also be used in the fabrication process to provide structural support for the stack when undoped polysilicon layers are removed by a wet etch and a dielectric is deposited to form the alternating dielectric layers. A dashed line **305** extends through columns C**12**-C**17**. A cross-sectional view along line **305** of portion **307** is shown in FIG. **3**C**1**.

Regions **340**, **341**, **342**, **343**, **344** and **345** represent the memory cells (as circles) of respective sets of NAND strings. For example, region **340** represents memory cells in NAND strings NS**0**A, . . . , NS**0**A-**14**. Additional NAND strings include NS**1**A, NS**2**A, NS**3**A, NS**4**A and NS**5**A.

Alternatively, the layer **304** represents an SGS layer, in which case each circle represents an SGS transistor.

FIG. **3**B depicts a top view of an example SGD layer **362**, consistent with FIG. **3**A. Slits **357**, **358**, **359**, **360** and **361** divide the SGD layer into portions **363**, **364**, **365**, **366**, **367** and **368**. Each portion connects the SGD transistors in a set of NAND strings. For example, SGD layer portion **363** or line connects the SGD transistors in the set of NAND strings NS**0**A to NS**0**A-**14**. Regions **351**, **352**, **353**, **354**, **355** and **356** represent the SGD transistors (as circles) of respective sets of NAND strings in the SGD layer portions **363**, **364**, **365**, **366**, **367** and **368**, respectively. The portion **307** from FIG. **3**A is also repeated. The select gate transistors are associated with NAND strings NS**0**A-NS**5**A.

FIG. **3C1** depicts an embodiment of a stack **376** showing a cross-sectional view of the portion **307** of FIG. **3**A, along line **305**, where three SGD layers, three SGS layers and dummy word line layers DWLL**1** and DWLL**2** are provided. Columns of memory cells corresponding to NAND strings NS**0**A-NS**3**A are depicted in the multi-layer stack. The stack includes a substrate **101**, an insulating film **250** on the substrate, and a portion of a source line SL**0**A. Additional straight NAND strings in a SGD line subset extend behind the NAND strings depicted in the cross-section, e.g., along the x-axis. NS**0**A has a source end SEa and a drain end DEa. The slits **346**, **347** and **348** from FIG. **3**A are also depicted. A portion of the bit line BL**0**A is also depicted. A conductive via **373** connects DEa to BL**0**A. The columns are formed in memory holes MH**0**-MH**4**. The memory holes are columnar and extend at least from a top **370** to a bottom **371** of the stack.

The source line SL**0**A is connected to the source ends of each NAND string. SL**0**A is also connected to other sets of memory strings which are behind these NAND strings in the x direction.

Word line layers, e.g., WLL**0**-WLL**23**, and dielectric layers, e.g., DL**0**-DL**24**, are arranged alternatingly in the stack. SGS transistors **369**, **372**, **374** and **375** are formed in the SGS**1** layer.

A region **246** of the stack is shown in greater detail in FIG. **4**A. Regions D**1***a*, D**2***a*, D**3***a* and D**4***a* represent SGD transistors.

FIG. **3C2** depicts a variation in the width of a memory hole along its height. Due to the etching process used to create the memory holes, the cross-sectional width, e.g., diameter, of the memory hole can vary along its height. This is due to the very high aspect ratio. For example, a depth-to-diameter ratio of about 25-30 is common. Typically, the diameter becomes progressively smaller from the top to the bottom of the memory hole. In some case, a slight narrowing occurs at the top of the hole, as depicted, so that the diameter becomes slight wider before becoming progressively smaller from the top to the bottom of the memory hole.

Due to the non-uniformity in the width of the memory hole, and the width of the vertical pillar which is formed in the memory hole, the programming and erase speed of the memory cells can vary based on their position along the memory hole. With a smaller diameter memory hole, the electric field across the tunneling layer is stronger, so that the programming and erase speed is higher.

In this case, the memory cells are arranged along vertically-extending memory holes (MH**0**-MH**7**) in the memory device, and a width of the vertically-extending memory holes varies along a height of the memory device.

FIG. **3**D depicts an alternative view of the select gate layers and word line layers of the stack **376** of FIG. **3**C. The SGD layers SGD**1** and SGD**2** each includes parallel rows of select gate lines associated with the drain-side of a set of NAND strings. For example, SGD**1** includes drain-side select gate lines **363**, **364**, **365**, **366**, **367** and **368**, consistent with FIG. **3**B. Each select gate line can be independently controlled, in one approach.

Below the SGD layers are the word line layers. Each word line layer represents a word line, in one approach, and is connected to a set of memory cells at a given height in the stack. For example, DWLL**3**, DWLL**4**, WLL**22**, WLL**21**, WLL**20** and WLL**19** represent word lines **399**, **398**, **397**, **396**, **395** and **394**, respectively. WLL**2**, WLL**1**, WLL**0** and DWLL**5** represent word lines **393**, **392**, **391** and **390**, respectively. Each word line can be controlled independently, in one approach.

Below the word line layers are the SGS layers. The SGS layers SGS**1** and SGS**2** each includes parallel rows of select gate lines associated with the source-side of a set of NAND strings. For example, SGS**1** includes source-side select gate lines **380**, **381**, **382**, **383**, **384** and **385**. Each select gate line can be independently controlled, in one approach.

In an example programming operation, the source-side word line **391** is a first programmed word line and a drain-side word line **397** is a final programmed word line in a block.

FIG. **4**A depicts a view of the region **246** of FIG. **3C1**, showing SGD transistors D**1***a*, D**1***a***1** and D**1***a***2** above a dummy memory cell (DMC) and a data-storing memory cell (MC). A number of layers can be deposited along the sidewalls of the column and within each word line layer. These layers can include oxide-nitride-oxide (O—N—O) and polysilicon layers which are deposited, e.g., using atomic layer deposition. For example, the column includes a charge-trapping layer or film (CTL) **403** such as SiN or other nitride, a tunneling layer (TL) **404**, a polysilicon body or channel (CH) **405**, and a dielectric core (DC) **406**. A word line layer includes a block oxide (BOx) **402**, a block high-k material **401**, a barrier metal **400**, and a conductive metal such as W **399** as a control gate. For example, control gates CG**1***a*, CG**1***a***1**, CG**1***a***2**, CG**1***a***3** and CG**1***a***4** are provided for the SGD transistors D**1***a*, D**1***a***1** and D**1***a***2**, the dummy memory cell DMC and the memory cell MC, respectively. In another approach, all of these layers except the metal are provided in the column. Additional memory cells are similarly formed throughout the columns. The layers in the memory hole form a columnar active area (AA) of the NAND string.

The use of one or more dummy memory cells between the select gate transistors and the data-storing memory cells is useful since program disturb can be greater for memory cells adjacent to, or close to, the select gate transistors. These edge cells have a lower amount of channel boosting due to constraints on the voltages of the select gate transistors of an inhibited NAND string. In particular, to provide the select gate transistors in a non-conductive state, a relatively low voltage is applied to their control gates, resulting in a relatively low amount of channel boosting in a region of the channel next to these select gate transistors. A region of the channel next to an edge cell will therefore also have a relatively low amount of channel boosting. In contrast, the memory cells next to a non-edge cell can receive a relatively high pass voltage since these cells are provided in a conductive state, resulting in a relatively higher amount of channel boosting.

When a memory cell is programmed, electrons are stored in a portion of the CTL which is associated with the memory cell. These electrons are drawn into the CTL from the channel, and through the tunneling layer (TL). The Vth of a memory cell is increased in proportion to the amount of stored charge. During an erase operation, the electrons return to the channel.

Each of the memory holes can be filled with a plurality of annular layers comprising a block oxide layer, a charge trapping layer, a tunneling layer and a channel layer. A core region of each of the memory holes is filled with a body material, and the plurality of annular layers are between the core region and the WLLs in each of the memory holes.

FIG. **4B1** depicts a cross-section view of the region **246** of FIG. **4**A along line **444**. Each layer is ring-shaped in one possible approach, except the core filler, which is a cylinder.

FIG. **4B2** depicts a close-up view of the tunneling layer **404** of FIG. **4B1**, showing an oxide **404***a*, nitride **404***b*, oxide **404***c* configuration.

FIG. **5**A depicts a process for performing a sensing operation on a selected word line, where a channel boosting voltage for an unselected NAND string is controlled based on a position of the selected word line. A sensing operation begins at step **500**. A sensing operation can include a read operation which determines the data state of a set of memory cells based on a read voltage which defines a lower Vth of the data state and a read voltage which defines an upper Vth of the data state, for example. This type of read operation occurs after a programming operation is completed. A sensing operation could also include a verify test which determines whether the Vth of a memory cell exceeds the verify voltage of a respective target data state during a programming operation. See FIG. **6** for example sensing voltages.

Step **501** includes identifying one or more selected NAND strings (e.g., NS_sel in FIG. **7**), one or more unselected NAND strings (e.g., NS_unsel in FIG. **7**), a selected word line (WLsel) and unselected word lines (WLunsel). For example, the selected NAND strings may be in a selected sub-block of memory cells (e.g., NS**0**A to NS**0**A-**14** associated with region **340** in FIG. **3**A), and the unselected NAND strings may be in one or more unselected sub-blocks of memory cells (e.g., NAND strings associated with regions **341**-**345** in FIG. **3**A). Each sub-block of NAND strings may have a common control line connected to their SGD transistors, for instance. The selected word line may be a selected word line layer in a stacked 3D memory device, and the unselected word lines may include the remaining word line layers.

Step **502** includes initializing the voltages including Vbl_sel, Vsl_sel, Vwl_sel, Vwl_unsel, Vsgd_sel, Vsgd_unsel, Vsgs_sel and Vsgs_unsel. Step **503** includes setting voltages for a channel boosting phase of the sensing operation. In this phase, the voltage in the channels of the unselected NAND strings is increased due to capacitive coupling from the increasing Vpass. The amount of capacitive coupling is proportional to the increase in Vpass while the channel is floated. Step **503** can be implemented using step **503***a*, which controls Vsgd_unsel, Vsgs_unsel, Vbl and/or Vsl based on a position of WLsel in NS_unsel.

Step **504** sets voltages for a sensing phase of the sensing operation, including a read voltage on WLsel. In this phase, the channel of the unselected NAND string may remain at, or close to, the boosted level which was set in the channel boosting phase. Step **505**, at a sense time, senses whether the Vth of the selected memory cells is above the read voltage. A decision step **506** determines whether there is a next read voltage to apply to WLsel. If decision step **506** is true, then step **504** is repeated with the next read voltage. If decision step **506** is false, the sensing operation ends at step **507**.

FIG. **5**B depicts a circuit diagram of an example memory cell such as the memory cell **705** of FIG. **7**. The memory cell includes a number of terminals including a drain (D) terminal which may have a voltage Vbl, a source (S) terminal which may have a voltage Vsl, a control gate (CG) terminal which may have a voltage Vcg and a channel (CH) terminal which may have a voltage Vch.

FIG. **6** depicts a threshold voltage (Vth) distribution and example read voltages for a set of memory cells, consistent with the process of FIG. **5**A. The horizontal axis represents Vth and the vertical axis represents a number of memory cells on a logarithmic scale. The Vth distributions are shown in a simplified form for clarity.

In one approach, a one programming pass operation, also referred to as full sequence programming, involves (only) one sequence of multiple program-verify operations (or program loops) which are performed starting from an initial Vpgm level and proceeding to a final Vpgm level until the threshold voltages of a set of selected memory cells reach one or more respective verify voltages of respective target data states. All memory cells may initially be in an erased state at the beginning of the programming pass.

Example Vth distributions for the memory cell array are provided for a case where each memory cell stores two bits of data in one of four possible Vth ranges. One bit represents the LP data and the other bit represents the UP data. A bit combination can be denoted by the UP bit followed by the LP bit, e.g., 11 denotes UP=1 and LP=1, 01 denotes UP=**0** and LP=1, 00 denotes UP=0 and LP=0 and 10 denotes UP=1 and LP=0. A bit combination is stored in a set of latches such as in FIG. **1**D. For example, the LP bit can be stored in LDL and the UP bit can be stored in UDL. In another example, each memory cell stores three bits of data in one of eight possible Vth ranges.

A first Vth distribution **795** is provided for erased (Er) state memory cells. Vth distributions **796**, **797** and **798** represent target data states A, B and C, respectively, which are reached by memory cells when their Vth exceeds the verify voltage VvA, VvB or VvC, respectively. VvEr is an erase verify voltage.

After the programming pass is completed, the data can be read from the memory cells using read reference voltages VrEr/A, VrA/B and VrB/C which are between the Vth distributions. By testing whether the Vth of a given memory cell is above or below one or more of the read reference voltages, the system can determine the data state which is represented by a memory cell.

FIG. **7** depicts a circuit diagram of a selected NAND string (NS_sel) and an unselected NAND string (NS_unsel), consistent with the sensing process of FIG. **5**A and with the memory devices of FIGS. **2**C and **3**C**1**. The word lines for data-storing memory cells are WLL**0**-WLL**22**. WLL**0**-WLL**22** are connected to data-storing memory cells **727**-**705**, respectively, in NS_sel and to data-storing memory cells **767**-**745**, respectively, in NS_unsel. Dummy word lines DWLL**1** and DWLL**2** are connected to dummy memory cells **704** and **728**, respectively, in NS_sel and to dummy memory cells **744** and **768**, respectively, in NS_unsel. The word lines are connected to both the selected and unselected NAND strings. Three SGD lines, SGD**1**_sel, SGD**2**_sel and SGD**3**_sel are connected to the SGD transistors **701**, **702** and **703**, respectively, in the selected NAND strings and, optionally, to one another. Three SGS lines, SGS**1**_sel, SGS**2**_sel and SGS**3**_sel are connected the SGS transistors **731**, **730** and **729**, respectively, in the selected NAND strings and, optionally, to one another. Three SGD lines, SGD**1**_unsel, SGD**2**_unsel and SGD**3**_unsel are connected to the SGD transistors **741**, **742** and **743**, respectively, in the unselected NAND strings and, optionally, to one another. Three SGS lines, SGS**1**_unsel, SGS**2**_unsel and SGS**3**_unsel are connected to the SGS transistors **771**, **770** and **769**, respectively, in the unselected NAND strings and, optionally, to one another.

I_NS_sel is a current in NS_sel. The current is sensed by sensing circuitry **700** via a bit line **780** which is at a voltage, Vbl. A channel of NS_sel is ch_sel and has a voltage of Vch_sel. A channel of NS_unsel is ch_unsel and has a voltage of Vch_unsel (also referred to as Vch).

A common bit line **780** connects the drain end of the NAND strings to the sensing circuitry, which is used to sense NS_sel during a sensing operation. A source line **781** is connected to source ends of the NAND strings. Voltage drivers can be used to provide voltages on the control lines (e.g., word lines, select gate lines, bit line and source line).

The memory cells in NS_unsel can be classified according to their position in the NAND string. For example, a subset **790** of memory cells **754-758** (or the associated subset of word lines WLL**13**-WLL**9**) is in a midrange of the NAND string, a subset **791** of memory cells **745-753** (or the associated subset of word lines WLL**22**-WLL**14**) is at a drain-side of the NAND string, and a subset **792** of memory cells **759-767** (or the associated subset of word lines WLL**8**-WLL**0**) is at a source-side of the NAND string.

The midrange may encompass a word line which is centered between the drain-end and the source-side of the unselected NAND string. Optionally, a number of word lines on either side of the center word line can be included as well, up to about 5-20% of all of the word lines. In one approach, a selected word line is midrange between the drain-end of the unselected NAND string and the source-side of the unselected NAND string when the selected word line is among a subset **790** of the multiple word lines which is centered between the drain-end of the unselected NAND string and the source-end of the unselected NAND string, the subset comprising up to about 10-20% of the multiple word lines.

The source-side may encompass up to about 30-40% of all of the word lines, for example. For example, a selected word line may be at the source-side of the unselected NAND string when the selected word line is among a source-side subset **792** of the multiple word lines which is adjacent to the source-end of the unselected NAND string, the source-side subset comprising up to 40% of the multiple word lines. Also, the selected word line may be at the drain-side of the unselected NAND string when the selected word line is among a drain-side subset (**791**) of the multiple word lines which is adjacent to the drain-end of the unselected NAND string, the drain-side subset comprising up to 40% of the multiple word lines.

More detailed classifications can be made as well. For example, a subset **791***a* encompasses memory cells **745-748** at a first portion of the drain-side of the NAND string, and a subset **791***b* encompasses memory cells **749-753** at a second portion of the drain-side of the NAND string, where the first portion is closer than the second portion to the drain-end of NS_unsel at the bit line. A subset **792***a* encompasses memory cells **759-763** at a first portion of the source-side of the NAND string, and a subset **792***b* encompasses memory cells **764-767** at a second portion of the source-side of the NAND string, where the first portion is closer than the second portion to the source-end of NS_unsel at the source line.

In FIGS. **8**A, **8**B, **10**, **11**A-**11**D, **13**A and **13**B, the horizontal axis depicts Vth in V and the vertical axis depicts a number of memory cells on a logarithmic scale. The upper tail of the Vth distribution of cells in the erased state is depicted.

FIG. **8**A depicts a plot of a Vth distribution for memory cells of WLsel+1, including a plot **800** where the SGS transistor is conductive and SGD is non-conductive, a plot **801** where the SGS and SGD transistors are non-conductive and the SGS transistor is underdriven by a smaller amount than the SGD transistor, and a plot **802** where the SGS and SGD transistors are non-conductive and the SGS transistor is underdriven by a same amount as the SGD transistor, where the amount of read stress is relatively small. The underdrive of a transistor is the gate bias minus the threshold voltage. For a transistor in the non-conductive state, the underdrive is typically a negative value. The underdrive is a measure of how strongly the transistor is cut off.

The data is from a midrange word line. A worst case condition was examined in which the memory cells of the unselected NAND strings on WLsel are in the highest programmed state, e.g., the C state, and the memory cells of the unselected NAND strings on WLsel−1 and WLsel+1 are in the erased state. The Vth distribution shown is for the unselected memory cells on WLsel+1 in the erased state. When the SGS transistor is conductive (plot **800**), there is a large amount of read disturb. However, when source-side is non-conductive, the HEI read disturb becomes lower (plot **801**). Moreover, the HEI read disturb becomes even lower (plot **802**) when the underdrive of the SGS transistor is stronger. A conclusion is that the HEI read disturb will be prominent if the SGD and SGS underdrive is not balanced, and the read disturb will exist on the side of the channel with the stronger underdrive.

FIG. **8**B depicts a plot of a Vth distribution similar to FIG. **8**A except that it is for memory cells of WLsel−1. This data is the counterpart to plots **801** and **802**, and shows that read disturb is very small for the unselected memory cells of WLsel−1 even when the read disturb is large for the unselected memory cells of WLsel+1.

FIG. **9**A depicts a plot of channel voltage (Vch) in an unselected NAND string, for a case where the SGS transistor is conductive and the SGD transistor is non-conductive, during the increase in Vpass. A time which is immediately after the increase in Vpass is depicted, when Vpass has reached its peak. The NAND string has a source end (SE) and a drain end (DE). FIG. **9**A to **9**D are aligned with one another. In FIGS. **9**A to **9**D, **12**A to **12**D and **14**A to **14**E, the horizontal axis depicts a position along the channel and the vertical axis depicts a voltage in the channel (Vch). The scale of the horizontal axis is such that the portions of the channel directly under WLsel−1, WLsel and WLsel+1, respectively, are emphasized. Additionally, circles with a "+" represent holes, circles with a "−" represent electrons and "x" represents a location of electron-hole generation due to a gradient in Vch.

The portions **900**, **901**, **902**, **903** and **904** of the channel are directly under WL**0** to WLsel−2, WLsel−1, WLsel, WLsel+1, and WLsel+2 to WL**22**, respectively. As an example, the memory cell connected to WLsel is in the highest programmed state, e.g., the C state, with a Vth of 4 V, and the memory cells connected to WLsel−1 and WLsel+1 are in the erased state, with a Vth of 0 V. Also, Vsl=0 V, Vwl_sel=0 V, and WL**0** to WLsel−1 and WLsel+1 to WL**22**−1 are increased from 0 V to 8 V according to Vpass. Since the SGS transistor is conductive and Vsl=0 V, the channel portions **900** and **901** are at Vch=0 V. Since the SGD transistor is non-conductive, the portions **903** and **904** of the channel are capacitively coupled up to 8 V, for instance, by the increase in Vpass. Moreover, the channel portion **902** has a low Vch, e.g., −4 V, due to Vwl_sel=0 V and Vth=0 V for the associated memory cell. In this case, the voltage in the portion of a channel directly under a memory cell is Vch=Vwl−Vth, where Vwl is the associated word line voltage and Vth is the Vth of the memory cell.

There is a gradient **910** in Vch between WLsel and WLsel+1 which causes electron-hole pairs to be generated in the channel. The electrons moves into the charge-trapping layer of the memory cell associated with WLsel+1, causing HEI read disturb. The holes move toward the channel portion **902**. This gradient is relatively large, having a magnitude of 8−(−4)=12 V. A gradient **911** in Vch is also formed in the channel between WLsel and WLsel−1, but this is of a smaller magnitude.

FIG. **9**B depicts a plot of Vch in the unselected NAND string of FIG. **9**A in a next moment in time (when Vpass has reached its peak). The holes move in the channel toward the source-side of WLsel−1 and the channel portion **902** is driven toward Vsl=0 V. Vch remains at a high level such as 7 V for the channel portion **903** and therefore continues to cause read disturb of the associated memory cells.

FIG. **9**C depicts a plot of Vch in an unselected NAND string, for a case where the SGS transistor and SGD transistor are non-conductive and are underdriven by a same amount, during the increase in Vpass. A time which is immediately after the increase in Vpass is depicted, when Vpass has reached its peak. The channel regions **900**, **901**, **903** and **904** are capacitively coupled higher due to the increase in Vpass. A channel gradient **920** causes electron-hole generation where the electrons and holes moved toward the channel portions **903** and **902**, respectively. Similarly, a channel gradient **921** causes electron-hole generation where the electrons and holes moved toward the channel portions **901** and **902**, respectively. HEI disturb occurs for the memory cells connected to WLwel+1 and WLsel−1.

FIG. **9**D depicts a plot of Vch in the unselected NAND string of FIG. **9**C, in a next moment in time. The Vch of the channel portion **902** combines with the Vch of the surrounding channel portions to form a uniform Vch, e.g., 7 V, throughout the length of the channel. Since there is no large gradient in Vch, there is no HEI read disturb.

Generally, in FIGS. **9**A and **9**C, holes fill in the channel portion **902** below WLsel very quickly since the channel capacitance of this single word line is relatively small compared to the capacitance of the entire channel. Electron injection occurs on the WLsel+1 side of WLsel in FIGS. **9**A and **9**B, or on both sides of WLsel in FIG. **9**C. Initially, at the end of the increase in Vpass, the read disturb is small since the elapsed time is small. However, after the channel portion **902** is filled by the holes, electron injection on WLsel+1 continues due to the existence of the Vch gradient **910** in FIG. **9**B. Since the capacitance on the channel portions **900**, **901**, **903** and **904** on the source and drain-sides of WLsel is much larger than the capacitance of the channel portion **902** under WLsel, additional time is needed to discharge the channel voltage, so the majority of the disturb occurs at this period of time. In contrast, in FIG. **9**D, no voltage gradient exists so no further electron injection occurs.

FIG. **10** depicts a plot of a Vth distribution for memory cells of various unselected word lines near a selected word line, for a case where the SGS transistor and SGD transistor are non-conductive and are underdriven by a same amount, where the amount of read stress is relatively large. WLn+1 to WLn+4 are word lines on the drain-side of WLsel (e.g., WLn) and WLn−1 to WLn−4 are word lines on the source-side of WLsel. Read stress occurs for memory cells as they experience read cycles, e.g., read operations. When the read stress (or total stress time) increases, disturb on both WLn+1 and WLn−1 becomes discernable (as indicated by a portion **810** of the plot). The fact that both WLn+1 and WLn−1 see the same amount of disturb indicates the electrons causing the disturb are from electron-hole generation due to the voltage gradient in the channel between WLn/WLn+1 and WLn/WLn−1. Memory cells of other word lines which are non-adjacent with WLsel do not see this disturb since both the drain-side and source-side remain boosted with some boosting voltage.

FIG. **11**A depicts a plot of a Vth distribution for memory cells of WLsel+1 (**1101**) and WLsel−1 (**1100**), where the selected word line (WLsel) is source-side, the SGS transistor and SGD transistor are non-conductive and are underdriven by a same amount, and the amount of read stress is relatively large. When WLsel is close to the source-side of the NAND strings (e.g., the data is for WL**3**), a worse disturb is observed on WLsel+1 than on WLsel−1.

FIG. **11**B depicts a plot of a Vth distribution for memory cells of WLsel+1 (**1111**) and WLsel−1 (**1110**) under similar conditions as in FIG. **11**A except that WLsel is midrange. For the midrange WL_sel (e.g., the data is for WL**11**), the boosting voltage on the source-side and drain-side is balanced since the channel capacitance on the source-side and drain-side is also balanced. This makes the disturb on WLn+1 and WLn−1 equal.

FIG. **11**C depicts a plot of a Vth distribution for memory cells of WLsel+1 (**1121**) and WLsel−1 (**1120**) under similar conditions as in FIG. **11**A except that WLsel is drain-side. When WLsel is close to the drain-side of the NAND strings (e.g., the data is for WL**19**), a worse disturb is observed on WLsel−1 than on WLsel+1. Thus, the disturb observed when stressing edge word lines can be significant.

FIG. **11**D depicts a plot of a Vth distribution for memory cells of WLsel+1 (**1130**) and WLsel−1 (**1131**), under similar conditions as in FIG. **11**A except that a spike is provided in Vwl_sel during the increase in Vpass. See also FIGS. **14**C to **14**E and **15**B. Due to the spike, the read disturb is increased for both WLsel−1 and WLsel+1. When the SGS and SGD transistors are cut off by the same under-drive, this reduces read disturb. However, a severe read disturb is still seen on edge word lines, and a spike in Vwl_sel does not improve the problem. A solution provided herein involves spiking Vsgd_unsel or Vsgs_unsel when WLsel is on the source or drain-side, respectively, of a NAND string. Spiking can be omitted when WLsel is midrange. This approach minimizes HEI read disturb for unselected memory cells on edge word lines or on word lines near the edge while also reducing the normal read disturb due to F-N tunneling on unselected memory cells of all word lines.

FIG. **12**A depicts a plot of Vch in the unselected NAND string of FIG. **9**A, in a next moment in time, where WLsel is source-side and there is no spike in Vsgd_unsel. FIG. **12**A to **12**D are aligned with one another. The portions **1200**, **1201**, **1202**, **1203** and **1204** of the channel are directly under WL**0** to WLsel−2, WLsel−1, WLsel, WLsel+1, and WLsel+2 to WL**22**, respectively. There is a gradient **1220** in Vch between WLsel and WLsel+1 which cause electron-hole pairs to be generated in the channel. The electrons moves into the charge-trapping layer of the memory cell associated with WLsel+1, causing HEI read disturb. The holes move toward the channel portions **1200** and **1201**, resulting in a lower Vch for those channel portions, while Vch remains fairly high, e.g., 7 V in the channel portions **1203** and **1204**. A large gradient **1220** therefore continues to generate electrons which disturb the memory cell associated with WLsel+1. The Vch for channel portions **1200** and **1201** is non-zero sue to some capacitive coupling.

FIG. **12**B depicts a plot of Vch in the unselected NAND string of FIG. **9**A, in a next moment in time, for a case where the SGS transistor and SGD transistor are non-conductive and are underdriven by a same amount, except that a spike is provided in Vsgd_unsel during the increase in Vpass, and where WLsel is source-side. The spike in Vsgd_unsel provides the SGD transistor in a conductive state briefly while Vpass is increasing, so that the capacitive coupling up of the channel portion on the drain-side of WLsel is temporarily halted. Additionally, the channel portion on the drain-side of WLsel will tend to move toward the voltage on the driven bit line. As a result, Vch for the channel portions **1203** and **1204** is lower when a spike in Vsgd_unsel is used than when a spike in Vsgd_unsel is not used. A small gradient **1230** in Vch might still exist in the channel between WLsel and WLsel+1, but it is insufficient to cause HEI disturb. Moreover, Vch can be positive and non-zero on the source and drain-sides of WLsel so that normal read disturb is also avoided. As an example, Vch=1 V for channel portions **1201** and **1202** and Vch=2 V for channel portions **1203** and **1204**. This demonstrates the

benefit of the spike. See FIG. **15**C for an example spiked waveform for an SGS or SGD transistor.

The drain-side of a word line, channel portion or memory cell refers to a side which is between the word line, channel portion or memory cell, respectively, and the drain end of the NAND string. The source-side of a word line, channel portion or memory cell refers to a side which is between the word line, channel portion or memory cell, respectively, and the source end of the NAND string.

FIG. **12**C depicts a plot of Vch in the unselected NAND string of FIG. **9**A, in a next moment in time, where WLsel is drain-side. The holes move toward the channel portions **1203** and **1204**, resulting in a lower Vch for those channel portions, while Vch remains fairly high, e.g., 7 V in the channel portions **1200** and **1201**. A large gradient **1240** continues to generate electrons which disturb the memory cell associated with WLsel−1.

FIG. **12**D depicts a plot of Vch in the unselected NAND string of FIG. **9**A, in a next moment in time, for a case where the SGS transistor and SGD transistor are non-conductive and are underdriven by a same amount, except that a spike is provided in Vsgs during the increase in Vpass, and where WLsel is drain-side. The spike in Vsgs_unsel provides the SGS transistor in a conductive state briefly while Vpass is increasing, so that the capacitive coupling up of the channel portion on the source-side of WLsel is temporarily halted. Additionally, the channel portion on the source-side of WLsel will tend to move toward the voltage on the driven source line. As a result, Vch for the channel portions **1200** and **1201** is lower when a spike in Vsgs_unsel is used than when a spike in Vsgs_unsel is not used. A small gradient **1250** in Vch might still exist in the channel between WLsel−1 and WLsel, but it is insufficient to cause HEI disturb. Moreover, Vch can be positive and non-zero on the source and drain-sides of WLsel so that normal read disturb is also avoided. As an example, Vch=2 V for channel portions **1201** and **1202** and Vch=1 V for channel portions **1204** and **1205**. This demonstrates the benefit of the spike.

FIG. **13**A depicts a plot of a Vth distribution for memory cells of WLsel+1 (**1300**) and WLsel−1 (**1301**), where WLsel is midrange, the SGS and SGD transistors are non-conductive and the SGS transistor is underdriven by a smaller amount than the SGD transistor, a spike is not provided in Vwl_sel during the increase in Vpass, and the amount of read stress is relatively small. When the SGS and SGD transistors are both non-conductive but with unbalanced underdrive, read disturb is prominent, even with low read stress. This demonstrates the benefit of a balanced underdrive.

FIG. **13**B depicts a plot of a Vth distribution for memory cells of WLsel+1 and WLsel−1 under similar conditions as in FIG. **13**A except that a spike is provided in Vwl_sel during the increase in Vpass. The spike in the waveform on WLsel can have a similar shape as the spike for Vsgs or Vsgd. See FIG. **15**B. A spike in Vwl_sel can substantially reduce HEI because it connects the channel voltage on the drain-side of WLsel to the channel voltage in the source-side of WLsel to balance out the voltages and reduce the Vch gradient. Read disturb is reduced, even with unbalanced underdrive of the SGS and SGD transistors.

FIG. **14**A depicts a plot of Vch in an unselected NAND string, for a case where the SGS and SGD transistors are non-conductive and the SGS transistor is underdriven by a smaller amount than the SGD transistor, during the increase in Vpass, where WLsel is midrange. FIG. **14**A to **14**E are aligned with one another. The portions **1400**, **1401**, **1402**, **1403** and **1404** of the channel are directly under WL**0** to WLsel−2, WLsel−1, WLsel, WLsel+1, and WLsel+2 to WL**22**, respectively. There is a gradient **1410** in Vch between WLsel and WLsel+1 which cause electron-hole pairs to be generated in the channel. The electrons moves into the charge-trapping layer of the memory cell associated with WLsel+1, causing HEI read disturb.

The holes move toward the channel portions **1400** and **1401**, resulting in a lower Vch (e.g., 4 V) for those channel portions, while Vch remains fairly high, e.g., 8 V in the channel portions **1403** and **1404**. The large gradient **1410** continues to generate electrons which disturb the memory cell associated with WLsel+1.

FIG. **14**B depicts a plot of Vch in the unselected NAND string of FIG. **14**A, in a next moment in time. The holes move in the channel toward the source-side of WLsel−1 and the channel portion **1402** is driven to a similar level as the channel portions **1400** and **1401**. Vch remains at a high level such as 7 V for the channel portion **1403** so that a fairly large gradient **1420** still exists which continues to cause read disturb of the associated memory cells.

FIG. **14**C depicts a plot of Vch in an unselected NAND string under similar conditions as in FIG. **14**A except that a spike is provided in Vwl_sel during the increase in Vpass. The plot represents a time in which the spike is applied, e.g., at a high level such as 8 V. For example, in the spike, Vwl_sel may transition from 0 V to 8 V and back to 0 V. Due to the temporarily higher Vwl_sel during the spike, Vch in channel portion **1402** is similar to Vch in the other channel portions. That is, the spike in Vwl_sel allows the source-side and drain-side channel portions to communicate, so that Vch is roughly equalized for the channel portions on the source-side and drain-side of WLsel at a level such as 4 V.

FIG. **14**D depicts a plot of Vch in the unselected NAND string of FIG. **14**C, at a first next moment in time. When Vwl_sel returns to 0 V after the spike, large gradients **1430** and **1431** in Vch are formed between WLsel and WLsel+1, and between WLsel and WLsel−1, respectively. Electron-hole pairs are generated from both gradients, where the electrons can temporarily cause disturb of the memory cells of WLsel−1 and WLsel+1.

FIG. **14**E depicts a plot of Vch in the unselected NAND string of FIG. **14**D, at a second next moment in time. Since the SGS transistor is underdriven by a smaller amount than the SGD transistor, a gradient **1440** will remain between WLsel and WLsel+1. However, it will be of a smaller magnitude than the gradients of FIG. **14**D so that HEI disturb is avoided. This shows that the spike in Vwl_sel is helpful when the underdrive of the SGS and SGD transistors is unbalanced.

FIG. **15**A depicts an example waveform in a sensing operation for Vwl_unsel, the voltage on unselected word lines. The horizontal axes in FIG. **15**A to **15**G depict time and are aligned. A boosting phase of a sensing operation occurs from t**2** to t**5**, when Vpass increases. The channel is then set at a boosted voltage (Vch) which remains in a sensing phase, from t**6** to t**11**. Vch is roughly fixed from t**5** to t**10** but may decay slightly.

Vwl_unsel is at 0 V from t**0**-t**2**, increases from 0 V to a peak level from t**2** to t**5** (plot **1500***a*), is at the peak level from t**5** to t**10** (plot **1500***b*) and decreases back down to 0 V at t**11** (plot **1500***c*). The increase in Vwl_unsel can be a controlled ramp up or a step increase. When Vwl_unsel=Vpass is applied to the unselected word lines, it provides the associated memory cells in a conductive state.

FIG. **15**B depicts an example waveform in a sensing operation for Vwl_sel, the voltage on the selected word line. Waveform **1510** depicts a spike in Vwl_sel. The spike increases at t**3** to a peak level of Vwl_sel max and decreases back to 0 V at t**4**. When the spike is applied to the selected word line, it

provides the associated memory cells in a conductive state. From t**7** to t**10**, Vwl_sel can be provided at one of three control gate read levels, for instance, as discussed in FIG. **6**. The example read levels are VrEr/A (plot **1513**), VrA/B (plot **1512**) and VrB/C (plot **1511**). In another example, Vwl_wel can be set to different levels in turn. For example, verify tests may be performed with Vwl_sel at VvA, then VvB and then VvC.

FIG. **15**C depicts an example waveform in a sensing operation for Vsgd_unsel, the voltage on an SGD transistor of an unselected NAND string, and Vsgs_unsel, the voltage on an SGS transistor of an unselected NAND string. Various options are possible. In one option, a waveform **1522** represents 0 V being applied from t**0** to t**11**. This represents the case without a voltage spike. In another option, a spike **1520** is applied from t**3** to t**4**. For example, the SGD transistor may have a voltage spike while the SGS transistor does not. Or, the SGS transistor may have a voltage spike while the SGD transistor does not. Or, both the SGD and SGS transistors may have a spike. A waveform **1521** represents another spike which has a smaller duration than the spike **1520**. The duration of the spike can be optimized (see FIG. **16**B). The spike reaches a peak level of Vsg_max which provides the associated transistors temporarily in a conductive state. Specifically, when the spike waveform is above the Vth of the SGD or SGS transistor, the SGD or SGS transistor is in a conductive state. The spike can occur any time during the increase in Vpass, e.g., at the start of the increase, e.g., from t**2** to t**3**, midrange through the increase, e.g., from t**3** to t**4**, or at the end of the increase, e.g., from t**4** to t**5**. It is even possible for multiple spikes to be used during the increase in Vpass.

A spike in Vsgd_unsel allows a driven voltage on the bit line (Vbl) to reach the channel of the unselected NAND string, while a spike in Vsgs_unsel allows a driven voltage on the source line (Vsl) to reach the channel of the unselected NAND string. That is, the bit line communicates with the drain-end of the channel when the SGD transistor is conductive, and the source line communicates with the source-end of the channel when the SGS transistor is conductive.

In one approach, if the selected word line is at a source-side of the unselected NAND string, the method includes controlling the drain-end select gate (SGD transistor) of the unselected NAND string to, at different times during the applying of the increasing voltage, allow a driven voltage on the bit line to reach the channel of the unselected NAND string (e.g., from t**3** to t**4**) and prevent the driven voltage on the bit line from reaching the channel of the unselected NAND string (e.g., from t**2** to t**3** and from t**4** to t**5**). Or, if the selected word line is at a drain-side of the unselected NAND string, controlling the source-end select gate (SGS transistor) of the unselected NAND string to, at different times during the applying of the increasing voltage, allow a driven voltage on a source line to reach the channel of the unselected NAND string (e.g., from t**3** to t**4**) and prevent the driven voltage on the source line from reaching the channel of the unselected NAND string (e.g., from t**2** to t**3** and from t**4** to t**5**).

For the unselected NAND strings, the select gates are in a non-conductive state during the sensing phase to avoid interfering with the sensing of the selected NAND strings.

FIG. **15**D depicts an example waveform **1530** in a sensing operation for Vsgd_sel, the voltage on an SGD transistor of a selected NAND string, and Vsgs_sel, the voltage on an SGS transistor of a selected NAND string. These transistors can be provided at a peak level of Vsg_max to provide the SGD and SGS transistors in a conductive state which allows sensing of the current in the selected NAND string.

FIG. **15**E depicts an example waveform in a sensing operation for Vbl, the voltage on a bit line which is connected to selected and unselected NAND strings, and Vch_sel, the voltage in the channel of a selected NAND string. Vbl**0** is a desired bit line voltage for the sensing phase. Generally, the sensing circuitry is configured to use this voltage as a baseline, where the sensing is based on a voltage decay from the baseline. In one approach (line **1540**), Vbl is at the same level during the boosting phase and the sensing phase. However, it is possible for Vbl to be higher (line **1541**) or lower (**1542**) during the boosting phase than in the sensing phase. For example, during the spike of Vsgd_unsel, a relatively higher Vbl can result in a relatively higher Vch and a relatively lower Vbl can result in a relatively lower Vch. Thus, Vbl can be optimized during the boosting phase, separately from the sensing phase, based on the position of WLsel.

T**9** is a sense time at which sensing circuitry associated with a selected NAND string determines a conductive state of the NAND string based on a current in the NAND string. Since Vwl_unsel causes the unselected memory cells in a NAND string to be in a conductive state, the conductive state of the NAND string as determined by sensing indicates the conductive state of the selected memory cell. With Vwl_sel applied to the selected memory cell, the conductive state of the NAND string indicates whether the Vth of the selected memory cell exceeds Vwl_sel. The NAND string is conductive if the Vth of the memory cell exceeds Vwl_sel. In one approach, Vbl decays below a level Vsense at t**9** when the string is conductive, as represented by waveform **1540***b* and this decay is sensed by the sensing circuitry. Waveform **1540***a* represents the case where the string is not conductive, in which case Vbl does not decay below Vsense.

Generally, the voltage in the channel of the selected NAND string, Vch_sel, is set to Vbl when the associated SGD transistor is in a conductive state.

FIG. **15**F depicts an example waveform in a sensing operation for Vsl, the voltage on a source line which is connected to selected and unselected NAND strings. Vsl**0** is a desired source line voltage for the sensing phase. In one approach (line **1550**), Vsl is at the same level during the boosting phase and the sensing phase. However, it is possible for Vsl to be higher (line **1551**) or lower (**1552**) during the boosting phase than in the sensing phase. During the spike of Vsgd_unsel, a relatively higher Vsl can result in a relatively higher Vch and a relatively lower Vsl can result in a relatively lower Vch. Thus, Vsl can be optimized during the boosting phase, separately from the sensing phase, based on the position of WLsel.

FIG. **15**G depicts an example waveform in a sensing operation for Vch_unsel, the voltage in the channel of an unselected NAND string. Vch_unsel, increases when Vpass increase due to capacitive coupling, as mentioned. During a spike in Vsgd_unsel or Vsgs_unsel, the coupling is temporarily halted so that Vch_unsel may decrease, remain constant, or increase at a slower rate than when the spike is not present. For example, waveform **1560** represents a case with no spike, where Vch_unsel reaches a high level of Vch**3** (which is too high and may cause a gradient which results in HEI disturb). Waveforms **1561**, **1562** and **1563** represent cases with a spike, where Vch_unsel reaches Vch**2**, Vch**1** or Vch**0**, respectively. The peak level of Vch_unsel can be optimized using factors such as spike duration, and the magnitude of Vbl and/or Vsl. Note also that the channel voltage can vary along the length of the channel. FIG. **15**G depicts a representative channel voltage.

In FIG. **16**A to **16**C, the horizontal axes are aligned and represent a position along the length of a channel of an unselected NAND string. The vertical axis represents a voltage.

Channel portions **1600** and **1601** are on a source-side of the unselected NAND string, channel portions **1603** and **1604** are on a drain-side of the unselected NAND string, and a channel portion **1602** is midrange in the unselected NAND string. As an example, the source-side is subdivided into regions such as a first source-side region **1600**, relatively close to the SE, and a second source-side region **1601**, relatively far from the SE. The drain-side is subdivided into regions such as a first drain-side region (channel portion **1604**), relatively close to the DE, and a second drain region (channel portion **1603**), relatively far from the DE. The channel portions **1600**, **1601**, **1602**, **1603** and **1604** may correspond to the word line subsets **792***b*, **792***a*, **790**, **791***b* and **791***a*, respectively, of FIG. **7**.

FIG. **16**A depicts a plot showing a select gate voltage in a sensing operation as a function of a position of WLsel, where a Vsgd_unsel spike but no Vsgs_unsel spike is used if WLsel is source-side, no Vsgd or Vsgs_unsel spike is used if WLsel is midrange and a Vsgs_unsel spike but no Vsgd_unsel spike is used if WLsel is drain-side. A plot **1640** represents Vsgd_unsel, and a plot **1642** represents Vsgs_unsel. Vsgd_unsel or Vsgs_unsel may have a peak value of Vsg_max, as discussed in connection with FIG. **15**C.

FIG. **16**B depicts a plot showing a spike duration (time t) of a select gate voltage in a sensing operation as a function of a position of WLsel, where a Vsgd_unsel spike is used having a variable duration but no Vsgs_unsel spike is used if WLsel is source-side, no Vsgd or Vsgs_unsel spike is used if WLsel is midrange and a Vsgs_unsel spike is used having a variable duration based, but no Vsgd_unsel spike is used if WLsel is drain-side. Plots **1620** and **1620***a* represent the Vsgd_unsel spike duration increasing gradually, or step-wise, respectively, in proportion to Dd, the distance of WLsel from DE, when WLsel is source-side. Plots **1622** and **1622***a* represent the Vsgs_unsel spike duration increasing gradually, or step-wise, respectively, in proportion to Ds, the distance of WLsel from SE, when WLsel is drain-side. Line **1623** represents no spike in Vsgd_unsel or Vsgs_unsel when WLsel is midrange.

Therefore, if WLsel is at the source-side of the unselected NAND string (e.g., WL subsets **792***b* and **792***a* of FIG. **7**, associated with channel portions **1600** and **1601**, respectively), the driven voltage on the bit line (Vbl) is allowed to reach the channel of the unselected NAND string for a duration during the applying of the increasing voltage (Vpass) which is inversely proportional to a distance (Ds) of the selected word line from the source-end of the unselected NAND string.

If WLsel is at the drain-side of the unselected NAND string, (e.g., WL subsets **791***b* and **791***a* of FIG. **7**, associated with channel portions **1603** and **1604**, respectively) the driven voltage on the source line (Vsl) is allowed to reach the channel of the unselected NAND string for a duration during the applying of the increasing voltage which is inversely proportional to a distance (Dd) of the selected word line from the drain-end of the unselected NAND string.

In the case of plot **1622***a*, the multiple word lines comprise different adjacent subsets of word lines; the selected word line is in one of the subsets of word lines; and if the selected word line is at the drain-side of the unselected NAND string, the driven voltage on the source line is allowed to reach the channel of the unselected NAND string for a duration (e.g., the duration of the spike in Vsgs_unsel) during the applying of the increasing voltage (Vpass) which is a function of a position of the one of the subsets among the different adjacent subsets.

In the case of plot **1620***a*, the multiple word lines comprise different adjacent subsets (**1600**, **1601**) of word lines; the selected word line is in one of the subsets of word lines; and if the selected word line is at the source-side of the unselected NAND string, the driven voltage on the bit line is allowed to reach the channel of the unselected NAND string for a duration (e.g., the duration of the spike in Vsgd_unsel) during the applying of the increasing voltage (Vpass) which is a function of a position of the one of the subsets among the different adjacent subsets.

FIG. **16**C depicts a plot showing a select gate voltage in a sensing operation as a function of a position of WLsel, where a Vsgd_unsel spike is used in which Vbl has a variable magnitude but no Vsgs_unsel spike is used if WLsel is source-side, no Vsgd or Vsgs_unsel spike is used if WLsel is midrange and a Vsgs_unsel spike is used in which Vsl has a variable magnitude but no Vsgd_unsel spike is used if WLsel is drain-side. Plots **1630** and **1630***a* represent the Vbl magnitude during a spike in Vsgd_unsel decreasing gradually, or step-wise, respectively, in proportion to Dd, the distance of WLsel from DE, when WLsel is source-side. Plots **1632** and **1632***a* represent the Vsl magnitude during a spike in Vsgs_unsel decreasing gradually, or step-wise, respectively, in proportion to Ds, the distance of WLsel from SE, when WLsel is drain-side. Line **1634** represents a fixed magnitude for Vbl and Vsl when WLsel is midrange and there is no spike in Vsgd_unsel or Vsgs_unsel.

Therefore, if the selected word line is at the source-side of the unselected NAND string, a magnitude of the driven voltage on the bit line (Vbl), when this voltage is allowed to reach the channel, of the unselected NAND string is proportional to a distance (Ds) of the selected word line from the source-end of the unselected NAND string.

If the selected word line is at the drain-side of the unselected NAND string, a magnitude of the driven voltage on the source line (Vsl), when this voltage is allowed to reach the channel of the unselected NAND string, is proportional to a distance (Dd) of the selected word line from the drain-end of the unselected NAND string.

In the case of plot **1632***a*, the multiple word lines comprise different adjacent subsets (**1603**, **1604**) of word lines; the selected word line is in one of the subsets of word lines; and if the selected word line is at the drain-side of the unselected NAND string, a magnitude of the driven voltage on the source line, when this voltage is allowed to reach the channel of the unselected NAND string, is set as a function of a position of the one of the subsets among the different adjacent subsets.

In the case of plot **1630***a*, the multiple word lines comprise different adjacent subsets (**1600**, **1601**) of word lines; the selected word line is in one of the subsets of word lines; and if the selected word line is at the source-side of the unselected NAND string, a magnitude of the driven voltage on the bit line, when this voltage is allowed to reach the channel of the unselected NAND string, is set as a function of a position of the one of the subsets among the different adjacent subsets.

Accordingly, it can be seen that, in one embodiment, a method for performing a sensing operation in a 3D stacked non-volatile memory device comprises: performing a boosting phase of the sensing operation, the boosting phase sets a boosting voltage of a channel of an unselected NAND string in the memory device, the unselected NAND string having a drain-end select gate at a drain-end of the unselected NAND string and a source-end select gate at a source-end of the unselected NAND string; after the boosting voltage is set, performing a sensing phase of the sensing operation, the sensing phase senses a current in a selected NAND string of the memory device, the selected NAND string having a drain-end select gate at a drain-end of the selected NAND string and a source-end select gate at a source-end of the selected NAND string; wherein: the memory device comprises multiple word

lines of memory cells including a selected word line and unselected word lines; and during the sensing phase, the current is sensed via a bit line which is connected to the drain-end of the selected NAND string and the drain-end of the unselected NAND string while one or more read voltages are applied to the selected word line; wherein the setting of the boosting voltage comprises: applying an increasing voltage to the unselected word lines; if the selected word line is at a source-side of the unselected NAND string, controlling the drain-end select gate of the unselected NAND string to, at different times during the applying of the increasing voltage, allow a driven voltage on the bit line to reach the channel of the unselected NAND string and prevent the driven voltage on the bit line from reaching the channel of the unselected NAND string; and if the selected word line is at a drain-side of the unselected NAND string, controlling the source-end select gate of the unselected NAND string to, at different times during the applying of the increasing voltage, allow a driven voltage on a source line to reach the channel of the unselected NAND string and prevent the driven voltage on the source line from reaching the channel of the unselected NAND string.

In another embodiment, a memory controller comprises: a storage device comprising a set of instructions, and a processor operable to execute the set of instructions. The set of instructions comprises: instructions to apply an increasing voltage to unselected memory cells in unselected word lines of a memory device in connection with a sensing operation involving a selected memory cell in a selected word line of the memory device, wherein the selected memory cell is in a selected NAND string of the memory device and unselected memory cells are in an unselected NAND string of the memory device; instructions to control a select gate of the unselected NAND string to, at different times during the applying of the increasing voltage, allow a driven voltage on a bit line to reach a channel of the unselected NAND string and prevent the driven voltage on the bit line from reaching the channel of the unselected NAND string, wherein the select gate is at a drain-end of the unselected NAND string if the selected word line is at a source-side of the unselected NAND string and the select gate is at a source-end of the unselected NAND string if the selected word line is at a drain-side of the unselected NAND string, wherein a boosting voltage is set in the channel of the unselected NAND string based on the control of the select gate; and instructions to sense a current in the selected NAND string via the bit line while the boosting voltage is set in the channel of the unselected NAND string.

In another embodiment, a 3D stacked non-volatile memory device comprises: multiple word lines of memory cells including a selected word line and unselected word lines; an unselected NAND string comprising a drain-end select gate at a drain-end of the unselected NAND string and a source-end select gate at a source-end of the unselected NAND string; a selected NAND string comprising a drain-end select gate at a drain-end of the selected NAND string and a source-end select gate at a source-end of the selected NAND string; a bit line which is connected to the drain-end of the selected NAND string and the drain-end of the unselected NAND string; and a control circuit. The control circuit is configured to: (a) perform a boosting phase of a sensing operation, the boosting phase sets a boosting voltage of a channel of the unselected NAND string, wherein to set the boosting voltage, the control circuit is configured to: (i) apply an increasing voltage to the unselected word lines, (ii) if the selected word line is at a source-side of the unselected NAND string, control the drain-end select gate of the unselected NAND string to, at different times during the increasing voltage, allow a driven voltage on the bit line to reach the channel of the unselected NAND string and prevent the driven voltage on the bit line from reaching the channel of the unselected NAND string, and (iii) if the selected word line is at a drain-side of the unselected NAND string, control the source-end select gate of the unselected NAND string to, at different times during the increasing voltage, allow a driven voltage on a source line to reach the channel of the unselected NAND string and prevent the driven voltage on the source line from reaching the channel of the unselected NAND string, and (b) after the boosting voltage is set, perform a sensing phase of the sensing operation, the sensing phase senses a current in the selected NAND string via the bit line while one or more read voltages are applied to the selected word line.

In another embodiment, a 3D stacked non-volatile memory device comprises: multiple word lines of memory cells including a selected word line and unselected word lines; an unselected NAND string comprising a drain-end select gate at a drain-end of the unselected NAND string and a source-end select gate at a source-end of the unselected NAND string; a selected NAND string comprising a drain-end select gate at a drain-end of the selected NAND string and a source-end select gate at a source-end of the selected NAND string; a selected memory cell connected to the selected word line, the selected memory cells is in the selected NAND string; unselected memory cells connected to the unselected word line, the unselected memory cells are in the selected NAND string and in the unselected NAND string; a bit line which is connected to the drain-end of the selected NAND string and the drain-end of the unselected NAND string; and a control circuit. The control circuit is configured to: apply an increasing voltage to the unselected memory cells via the unselected word lines in connection with a sensing operation involving the selected memory cell; during one portion of a time period in which the increasing voltage occurs, control the drain-end select gate of the unselected NAND string and the source-end select gate of the unselected NAND string to float a voltage of a channel of the unselected NAND string, to allow the voltage of the channel to increase due to capacitive coupling from the increasing voltage; during another portion of the time period in which the increasing voltage occurs, if the selected word line is at a source-side of the unselected NAND string, control the drain-end select gate end of the unselected NAND string to connect the channel of the unselected NAND string to a driven voltage on the bit line, to prevent an increase in the voltage of the channel of the unselected NAND string due to capacitive coupling, wherein the driven voltage on the bit line is connected to the channel of the unselected NAND string for a duration during the time period in which the increasing voltage occurs, and the duration is inversely proportional to a distance of the selected word line from the source-end of the unselected NAND string; and after the time period, sense a current in the selected NAND string via the bit line.

The foregoing detailed description of the invention has been presented for purposes of illustration and description. It is not intended to be exhaustive or to limit the invention to the precise form disclosed. Many modifications and variations are possible in light of the above teaching. The described embodiments were chosen in order to best explain the principles of the invention and its practical application, to thereby enable others skilled in the art to best utilize the invention in various embodiments and with various modifications as are suited to the particular use contemplated. It is intended that the scope of the invention be defined by the claims appended hereto.

What is claimed is:

1. A method for performing a sensing operation in a non-volatile memory device, the method comprising:

performing a boosting phase of the sensing operation, the boosting phase sets a boosting voltage of a channel of an unselected NAND string in the memory device, the unselected NAND string comprising a drain-end select gate at a drain-end of the unselected NAND string and a source-end select gate at a source-end of the unselected NAND string;

after the boosting voltage is set, performing a sensing phase of the sensing operation, the sensing phase senses a current in a selected NAND string of the memory device, the selected NAND string comprising a drain-end select gate at a drain-end of the selected NAND string and a source-end select gate at a source-end of the selected NAND string; wherein:

the memory device comprises multiple word lines of memory cells including a selected word line and unselected word lines;

the selected NAND string and the unselected NAND strings each comprise a charge-trapping layer and a polysilicon channel layer which extend vertically in a three-dimensional stacked memory structure; and

during the sensing phase, the current is sensed via a bit line which is connected to the drain-end of the selected NAND string and the drain-end of the unselected NAND string while one or more read voltages are applied to the selected word line;

wherein the performing the boosting phase comprises:

applying an increasing voltage to the unselected word lines;

if the selected word line is at a source-side of the unselected NAND string, controlling the drain-end select gate of the unselected NAND string to, at different times during the applying of the increasing voltage, allow a driven voltage on the bit line to reach the channel of the unselected NAND string by providing the drain-end select gate of the unselected NAND string in a conductive state and prevent the driven voltage on the bit line from reaching the channel of the unselected NAND string by providing the drain-end select gate of the unselected NAND string in a non-conductive state;

if the selected word line is at a drain-side of the unselected NAND string, controlling the source-end select gate of the unselected NAND string to, at different times during the applying of the increasing voltage, allow a driven voltage on a source line to reach the channel of the unselected NAND string by providing the source-end select gate of the unselected NAND string in a conductive state and prevent the driven voltage on the source line from reaching the channel of the unselected NAND string by providing the source-end select gate of the unselected NAND string in a non-conductive state; and

if the selected word line is midrange between the drain-end of the unselected NAND string and the source-end of the unselected NAND string, preventing the driven voltage on the bit line from reaching the channel of the unselected NAND string throughout the applying of the increasing voltage by providing the drain-end select gate of the unselected NAND string in a non-conductive state, and preventing the driven voltage on the source line from reaching the channel of the unselected NAND string throughout the applying of the increasing voltage by providing the source-end select gate of the unselected NAND string in a non-conductive state.

2. The method of claim 1, wherein:

the selected word line is midrange between the drain-end of the unselected NAND string and the source-side of the unselected NAND string when the selected word line is among a subset of the multiple word lines which is centered between the drain-end of the unselected NAND string and the source-end of the unselected NAND string, the subset comprising up to 20% of the multiple word lines.

3. The method of claim 1, further comprising:

if the selected word line is at the source-side of the unselected NAND string, providing memory cells connected to the selected word line in a conductive state while the driven voltage on the bit line is allowed to reach the channel of the unselected NAND string; and

if the selected word line is at the drain-side of the unselected NAND string, providing the memory cells connected to the selected word line in the conductive state while the driven voltage on the source line is allowed to reach the channel of the unselected NAND string.

4. The method of claim 1, further comprising:

if the selected word line is at the source-side of the unselected NAND string, providing the source-end select gate of the unselected NAND string in a non-conductive state to prevent the driven voltage on the source line from reaching the channel of the unselected NAND string throughout the applying of the increasing voltage.

5. The method of claim 1, further comprising:

if the selected word line is at the drain-side of the unselected NAND string, providing the drain-end select gate of the unselected NAND string in a non-conductive state to prevent the driven voltage on the bit line from reaching the channel of the unselected NAND string throughout the applying of the increasing voltage.

6. The method of claim 1, wherein:

the selected word line is at the source-side of the unselected NAND string when the selected word line is among a source-side subset of the multiple word lines which is adjacent to the source-end of the unselected NAND string, the source-side subset comprising up to 40% of the multiple word lines; and

the selected word line is at the drain-side of the unselected NAND string when the selected word line is among a drain-side subset of the multiple word lines which is adjacent to the drain-end of the unselected NAND string, the drain-side subset comprising up to 40% of the multiple word lines.

7. The method of claim 1, wherein:

if the selected word line is at the source-side of the unselected NAND string, the driven voltage on the bit line is allowed to reach the channel of the unselected NAND string for a duration during the applying of the increasing voltage which is inversely proportional to a distance of the selected word line from the source-end of the unselected NAND string.

8. The method of claim 1, wherein:

if the selected word line is at the drain-side of the unselected NAND string, the driven voltage on the source line is allowed to reach the channel of the unselected NAND string for a duration during the applying of the increasing voltage which is inversely proportional to a distance of the selected word line from the drain-end of the unselected NAND string.

9. The method of claim 1, wherein:

if the selected word line is at the source-side of the unselected NAND string, a magnitude of the driven voltage on the bit line when the driven voltage on the bit line is allowed to reach the channel of the unselected NAND string is proportional to a distance of the selected word line from the source-end of the unselected NAND string.

10. The method of claim 1, wherein:

if the selected word line is at the drain-side of the unselected NAND string, a magnitude of the driven voltage on the source line when the driven voltage on the source line is allowed to reach the channel of the unselected NAND string is proportional to a distance of the selected word line from the drain-end of the unselected NAND string.

11. The method of claim 1, wherein:

the multiple word lines comprise different adjacent subsets of word lines;

the selected word line is in one of the subsets of word lines; and

if the selected word line is at the source-side of the unselected NAND string, the driven voltage on the bit line is allowed to reach the channel of the unselected NAND string for a duration during the applying of the increasing voltage which is a function of a position of the one of the subsets among the different adjacent subsets.

12. The method of claim 1, wherein:

the multiple word lines comprise different adjacent subsets of word lines;

the selected word line is in one of the subsets of word lines; and

if the selected word line is at the source-side of the unselected NAND string, a magnitude of the driven voltage on the bit line when the driven voltage on the bit line is allowed to reach the channel of the unselected NAND string is set as a function of a position of the one of the subsets among the different adjacent subsets.

13. The method of claim 1, wherein:

the multiple word lines comprise different adjacent subsets of word lines;

the selected word line is in one of the subsets of word lines; and

if the selected word line is at the drain-side of the unselected NAND string, the driven voltage on the source line is allowed to reach the channel of the unselected NAND string for a duration during the applying of the increasing voltage which is a function of a position of the one of the subsets among the different adjacent subsets.

14. The method of claim 1, wherein:

the multiple word lines comprise different adjacent subsets of word lines;

the selected word line is in one of the subsets of word lines; and

if the selected word line is at the drain-side of the unselected NAND string, a magnitude of the driven voltage on the source line when the driven voltage on the source line is allowed to reach the channel of the unselected NAND string is set as a function of a position of the one of the subsets among the different adjacent subsets.

15. A memory controller, comprising:

a storage device comprising a set of instructions, the set of instructions comprising:

instructions to apply an increasing voltage to unselected memory cells in unselected word lines of a memory device in connection with a sensing operation involving a selected memory cell in a selected word line of the memory device, wherein the selected memory cell is in a selected NAND string of the memory device, unselected memory cells are in an unselected NAND string of the memory device, the unselected NAND string comprising a drain-end select gate at a drain-end of the unselected NAND string and a source-end select gate at a source-end of the unselected NAND string;

instructions to, —if the selected word line is at a source-side of the unselected NAND string, control the drain-end select gate of the unselected NAND string to, at different times during the applying of the increasing voltage, allow a driven voltage on a bit line to reach a channel of the unselected NAND string by providing the drain-end select gate in a conductive state and prevent the driven voltage on the bit line from reaching the channel of the unselected NAND string by providing the drain-end select gate in a non-conductive state;

instructions to, if the selected word line is at a drain-side of the unselected NAND string, control the source-end select gate of the unselected NAND string to, at different times during the applying of the increasing voltage, allow a driven voltage on a source line to reach the channel of the unselected NAND string by providing the source-end select gate in a conductive state and prevent the driven voltage on the source line from reaching the channel of the unselected NAND string by providing the source-end select gate in a non-conductive state;

instructions to, if the selected word line is midrange between the drain-end of the unselected NAND string and the source-end of the unselected NAND string, prevent the driven voltage on the bit line from reaching the channel of the unselected NAND string throughout the applying of the increasing voltage by providing the drain-end select gate of the unselected NAND string in a non-conductive state, and preventing the driven voltage on the source line from reaching the channel of the unselected NAND string throughout the applying of the increasing voltage by providing the source-end select gate of the unselected NAND string in a non-conductive state; and

instructions to sense a current in the selected NAND string via the bit line while a boosting voltage is set in the channel of the unselected NAND string; and a processor operable to execute the set of instructions.

16. The memory controller of claim 15, wherein the set of instructions further comprises:

instructions to allow the driven voltage on the bit line to reach the channel of the unselected NAND string for a duration during the applying of the increasing voltage which is inversely proportional to a distance of the selected word line from the source-end of the unselected NAND string, if the selected word line is at the source-side of the unselected NAND string.

17. The memory controller of claim 15, wherein the set of instructions further comprises:

instructions to allow the driven voltage on the source line to reach the channel of the unselected NAND string for a duration during the applying of the increasing voltage which is inversely proportional to a distance of the selected word line from the drain-end of the unselected NAND string, if the selected word line is at the drain-side of the unselected NAND string.

18. A 3D stacked non-volatile memory device, comprising:

multiple word lines of memory cells including a selected word line and unselected word lines;

an unselected NAND string comprising a drain-end select gate at a drain-end of the unselected NAND string and a source-end select gate at a source-end of the unselected NAND string;

a selected NAND string comprising a drain-end select gate at a drain-end of the selected NAND string and a source-end select gate at a source-end of the selected NAND string;

a selected memory cell connected to the selected word line, the selected memory cells is in the selected NAND string;

unselected memory cells connected to the unselected word line, the unselected memory cells are in the selected NAND string and in the unselected NAND string;

a bit line which is connected to the drain-end of the selected NAND string and the drain-end of the unselected NAND string; and

a control circuit, the control circuit is configured to:

apply an increasing voltage to the unselected memory cells via the unselected word lines in connection with a sensing operation involving the selected memory cell;

during one portion of a time period in which the increasing voltage occurs, provide the drain-end select gate of the unselected NAND string and the source-end select gate of the unselected NAND string in a non-conductive state to float a voltage of a channel of the unselected NAND string;

during another portion of the time period in which the increasing voltage occurs, if the selected word line is at a source-side of the unselected NAND string, provide the drain-end select gate end of the unselected NAND string in a conductive state to connect the channel of the unselected NAND string to a driven voltage on the bit line, wherein the driven voltage on the bit line is connected to the channel of the unselected NAND string for a duration during the time period in which the increasing voltage occurs, and the duration is inversely proportional to a distance of the selected word line from the source-end of the unselected NAND string; and

after the time period, sense a current in the selected NAND string via the bit line.

19. The 3D stacked non-volatile memory device of claim **18**, wherein the control circuit is configured to:

during the another portion of the time period in which the increasing voltage occurs, if the selected word line is at a drain-side of the unselected NAND string, control the source-end select gate of the unselected NAND string to connect the channel of the unselected NAND string to a driven voltage on a source line.

20. The 3D stacked non-volatile memory device of claim **19**, wherein the control circuit is configured to:

if the selected word line is at the drain-side of the unselected NAND string, connect the driven voltage on the source line to the channel of the unselected NAND string for a duration during the time period in which the increasing voltage occurs, where the duration is inversely proportional to a distance of the selected word line from the drain-end of the unselected NAND string.

21. An apparatus, comprising:

multiple word lines of memory cells including a selected word line and unselected word lines;

an unselected string of the memory cells;

a selected string of the memory cells, the selected string and the unselected strings each comprise a charge-trapping layer and a polysilicon channel layer which extend vertically in a three-dimensional stacked memory structure;

means for performing a boosting phase of the sensing operation, the boosting phase sets a boosting voltage of a channel of an unselected string of the memory cells, the unselected string comprising a drain-end select gate at a drain-end of the unselected string and a source-end select gate at a source-end of the unselected string; and

means for, after the boosting voltage is set, performing a sensing phase of the sensing operation, the sensing phase senses a current in a selected string of the memory cells, the selected NAND string comprising a drain-end select gate at a drain-end of the selected NAND string and a source-end select gate at a source-end of the selected NAND string, wherein during the sensing phase, the current is sensed via a bit line which is connected to the drain-end of the selected string and the drain-end of the unselected string while one or more read voltages are applied to the selected word line;

wherein the means for performing a boosting phase comprises:

means for applying an increasing voltage to the unselected word lines;

means for, if the selected word line is at a source-side of the unselected string, controlling the drain-end select gate of the unselected string to, at different times during the applying of the increasing voltage, allow a driven voltage on the bit line to reach the channel of the unselected string by providing the drain-end select gate of the unselected string in a conductive state and prevent the driven voltage on the bit line from reaching the channel of the unselected string by providing the drain-end select gate of the unselected string in a non-conductive state;

means for, if the selected word line is at a drain-side of the unselected string, controlling the source-end select gate of the unselected string to, at different times during the applying of the increasing voltage, allow a driven voltage on a source line to reach the channel of the unselected string by providing the source-end select gate of the unselected string in a conductive state and prevent the driven voltage on the source line from reaching the channel of the unselected string by providing the source-end select gate of the unselected string in a non-conductive state; and

means for, if the selected word line is midrange between the drain-end of the unselected string and the source-end of the unselected string, preventing the driven voltage on the bit line from reaching the channel of the unselected string throughout the applying of the increasing voltage by providing the drain-end select gate of the unselected string in a non-conductive state throughout the applying of the increasing voltage, and preventing the driven voltage on the source line from reaching the channel of the unselected string, throughout the applying of the increasing voltage by providing the source-end select gate of the unselected string in a non-conductive state.

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